

# Load-pull techniques for 5G and 6G applications – state of the art and future

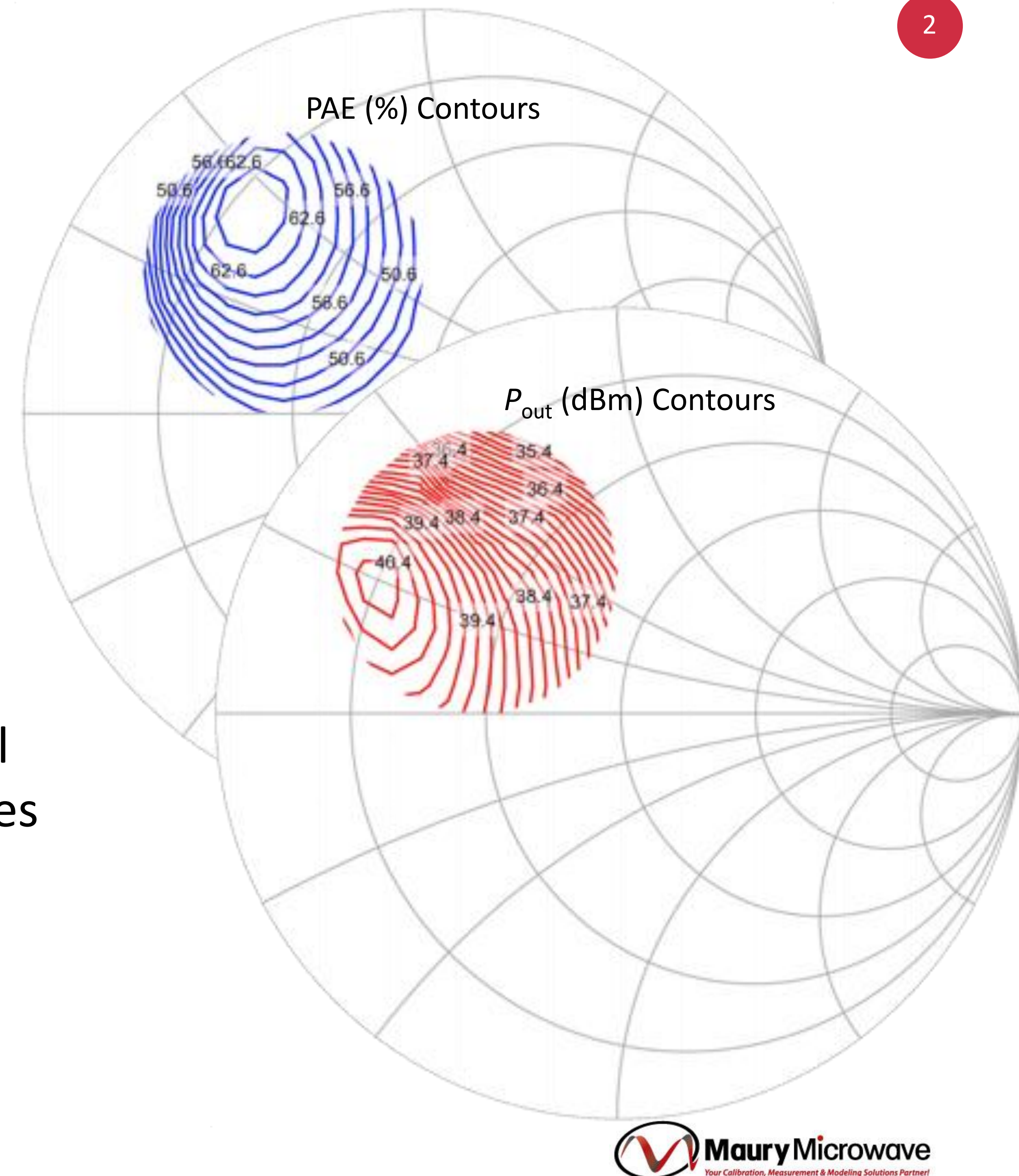
Mauro Marchetti



# ●●●● Motivation for Load pull

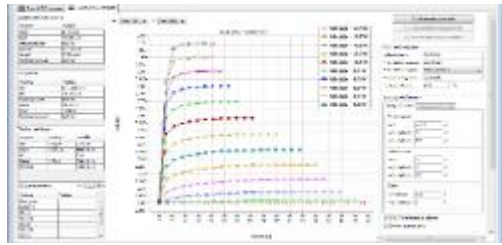
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- S-parameters provide information about linear response of the device under test (DUT)
- Transistor performance is highly dependent on its load impedance
- RF/Microwave transistors exhibit non-linear behavior:
  - harmonic generation
  - frequency mixing, etc.
- Load-pull enables characterisation of the linear and non-linear DUT behaviour under large-signal excitations and non-50  $\Omega$  source/load impedances

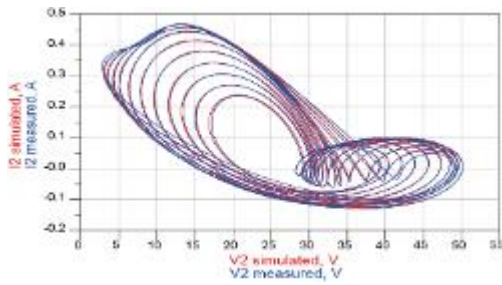


# ●●●●● Load pull and source pull applications

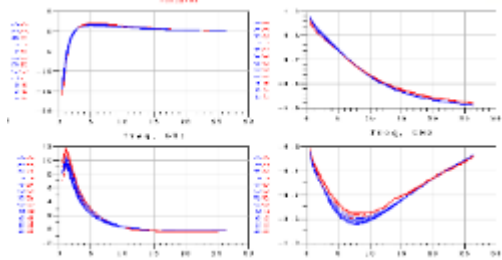
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Transistor characterization



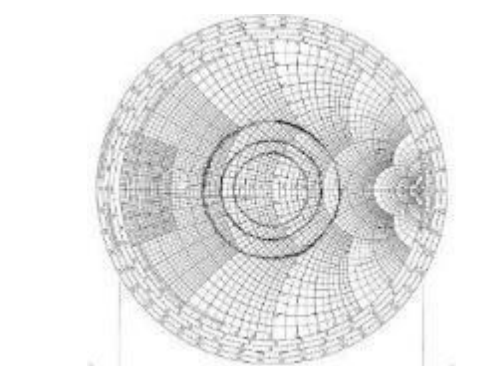
Compact transistor model validation



Behavioral model extraction



Matching network design (PA, LNA...)



Performance test / reliability test



# ●●●● Bandwidth Requirements by Application

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Application	Frequency Range	Single Channel Bandwidth	Total Bandwidth (1 Channel + ACLR)	Optimum Channels For Test	Total Bandwidth (n Channels + ACLR)
W-CDMA	800 MHz – 3.5 GHz	5 MHz	15 MHz	5	25 MHz
Multi-carrier W-CDMA	800 MHz – 3.5 GHz	15 MHz	25 MHz	7	35 MHz
LTE	600 MHz – 6 GHz	20 MHz	60 MHz	5	100 MHz
802.11a/b/g	2.4 GHz	20 MHz	60 MHz	5	100 MHz
802.11n	2.4 GHz, 5 GHz	40 MHz	160 MHz	5	200 MHz
LTE-A	800 MHz – 3.5 GHz	100 MHz	300 MHz	5	500 MHz
802.11ac	5 GHz	160 MHz	480 MHz	3	480 MHz
802.11ax	2.4 / 5 GHz	160 MHz	480 MHz	3	480 MHz
5G	600 MHz – 6 GHz	100 MHz	300 MHz	4	600 MHz
5G	28 GHz	400 MHz			
5G	38 GHz	~1 GHz			
6G	95 GHz – 3 THz ???				

# ●●●● 5G (and 6G) Challenges for load pull

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Higher frequencies → higher losses

Higher bandwidth → modulated signals characterization,  
phase skew

Higher PAR → higher dynamic range

Higher level of integration → new test requirements

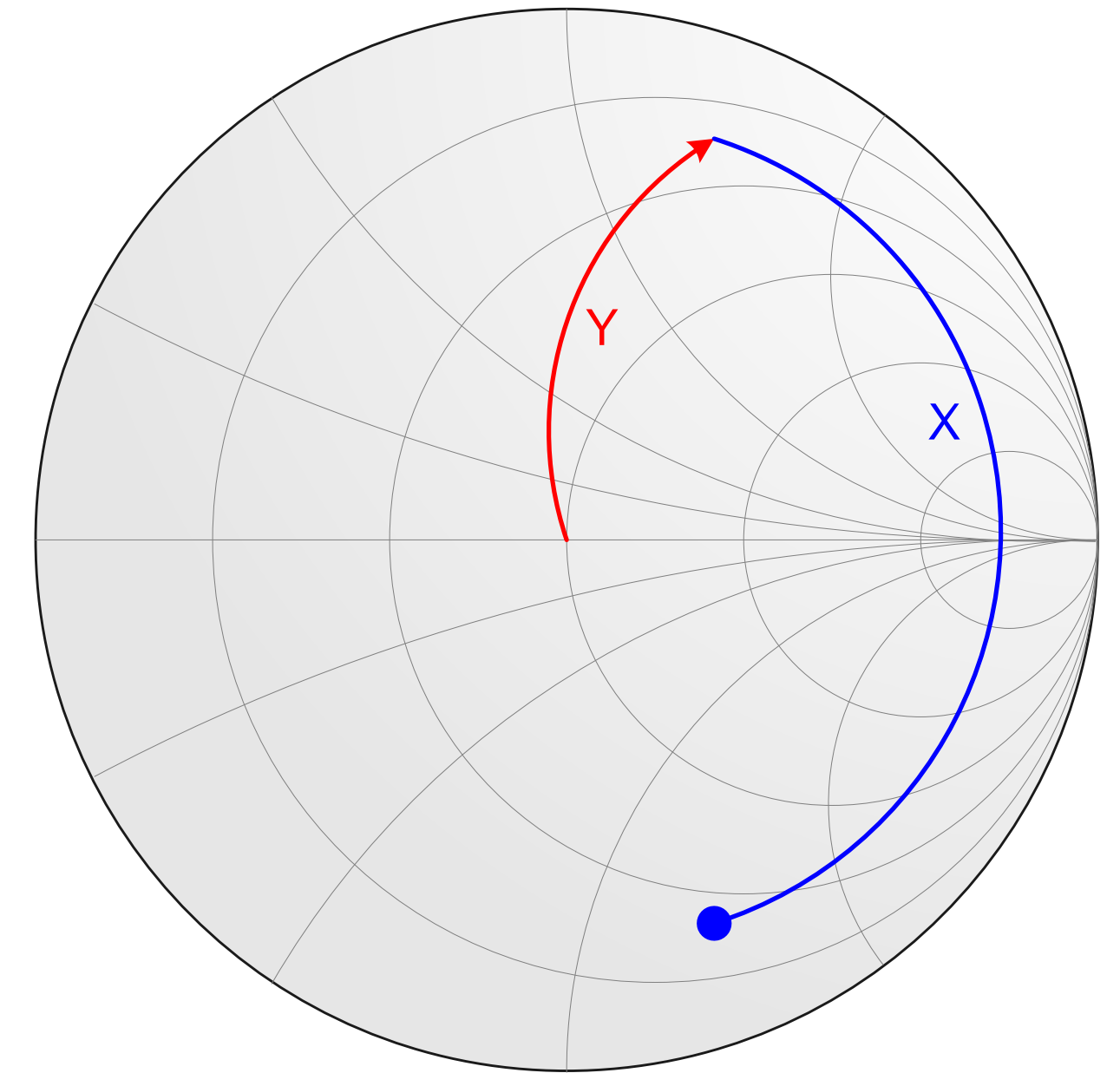
# Passive tuning



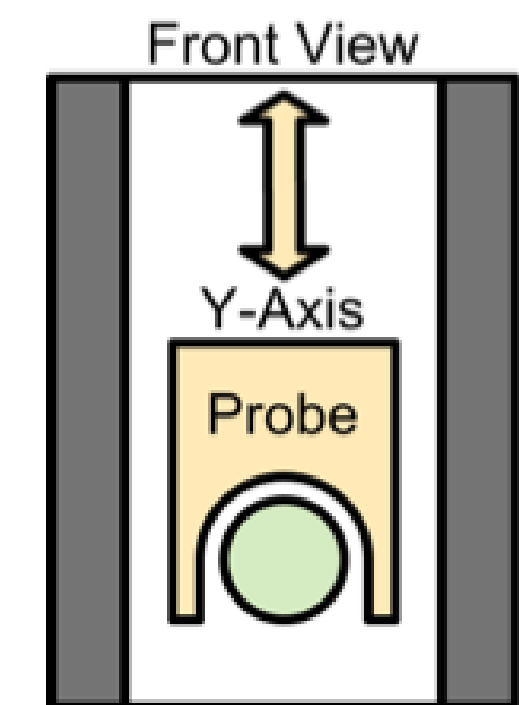
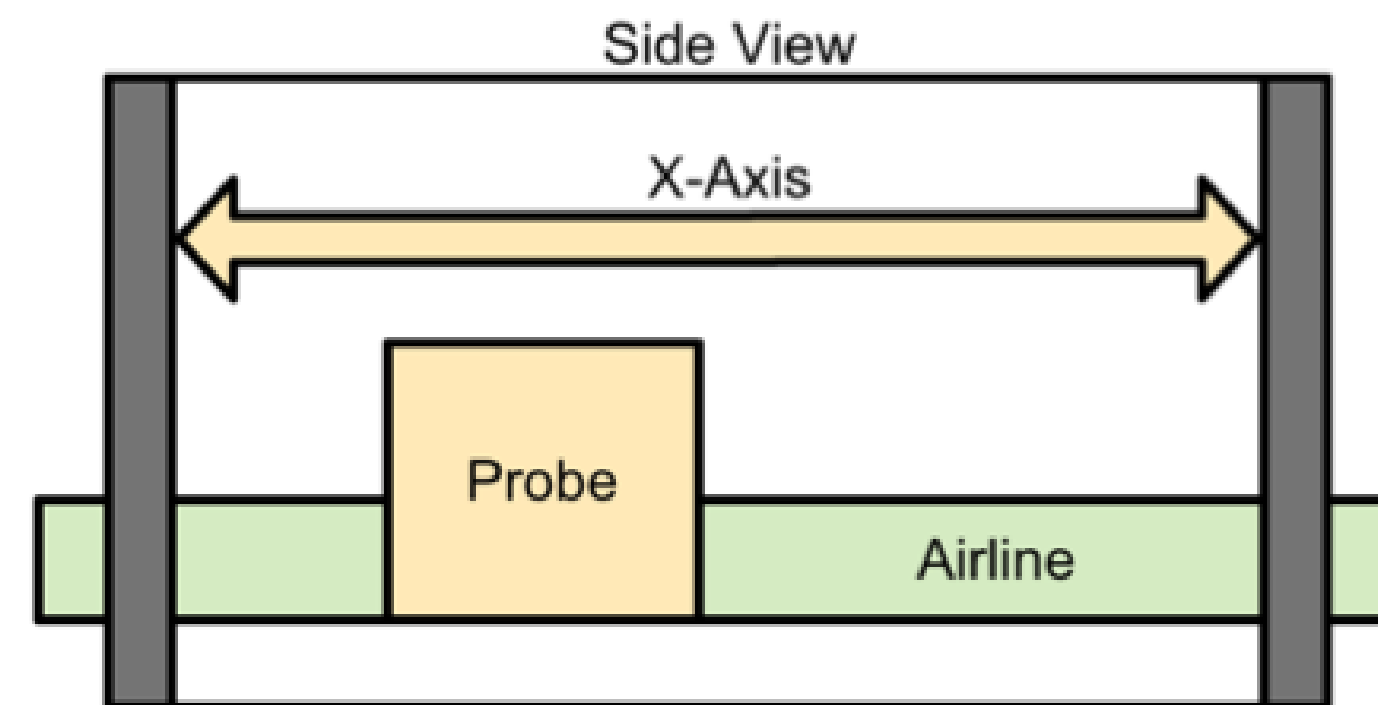
# Slide-screw impedance tuners

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- Probe movement above airline controls the reflection coefficient ( $\Gamma$ )
- Movement on  $X$ -axis controls phase of  $\Gamma$
- Movement on  $Y$ -axis controls magnitude of  $\Gamma$
- $|\Gamma|$  is always less than 1 as tuner introduces dissipative loss
- Loss increases with frequency thus  $\Gamma$  tunable range shrinks



$$\Gamma_{Load,n}(f_n) = \frac{a_{2,n}(f_n)}{b_{2,n}(f_n)}$$



# ●●●● Important considerations

- **Speed:**
  - DVT applications require hundreds of measurements to cover different signal bands and modulation types. Tuning speed is essential
- **Accuracy:**
  - Check and balance to gain confidence in your data
- **On wafer measurements:**
  - Adding components in front of the tuner element will:
    - Reduce the tuning range at the DUT reference
    - Increase the phase skew of the selected impedance against the signal BW

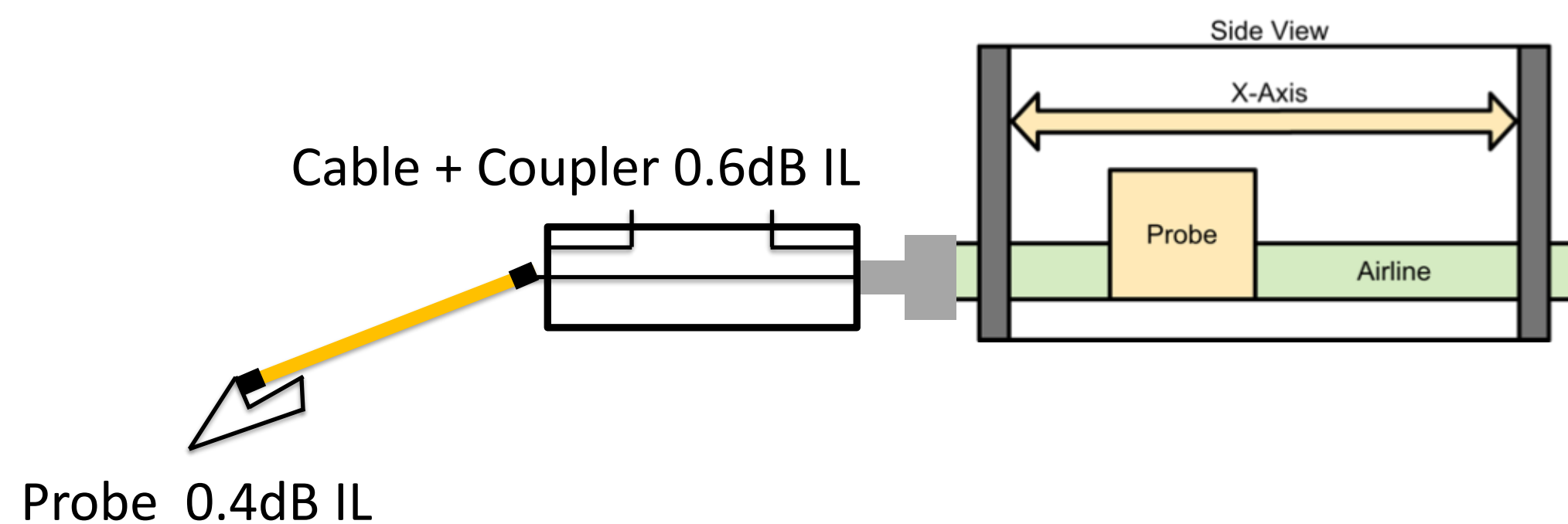


# ●●●● Tuning range

Frequency

28 GHz

- $VSWR_{tuner} = 15:1 \rightarrow |\Gamma_{tuner}| = 0.87$
- $IL_{coupler + cable + probe} = 1 \text{ dB}$
- $VSWR_{Load} = 5.6:1 \rightarrow |\Gamma_{load}| = 0.69$



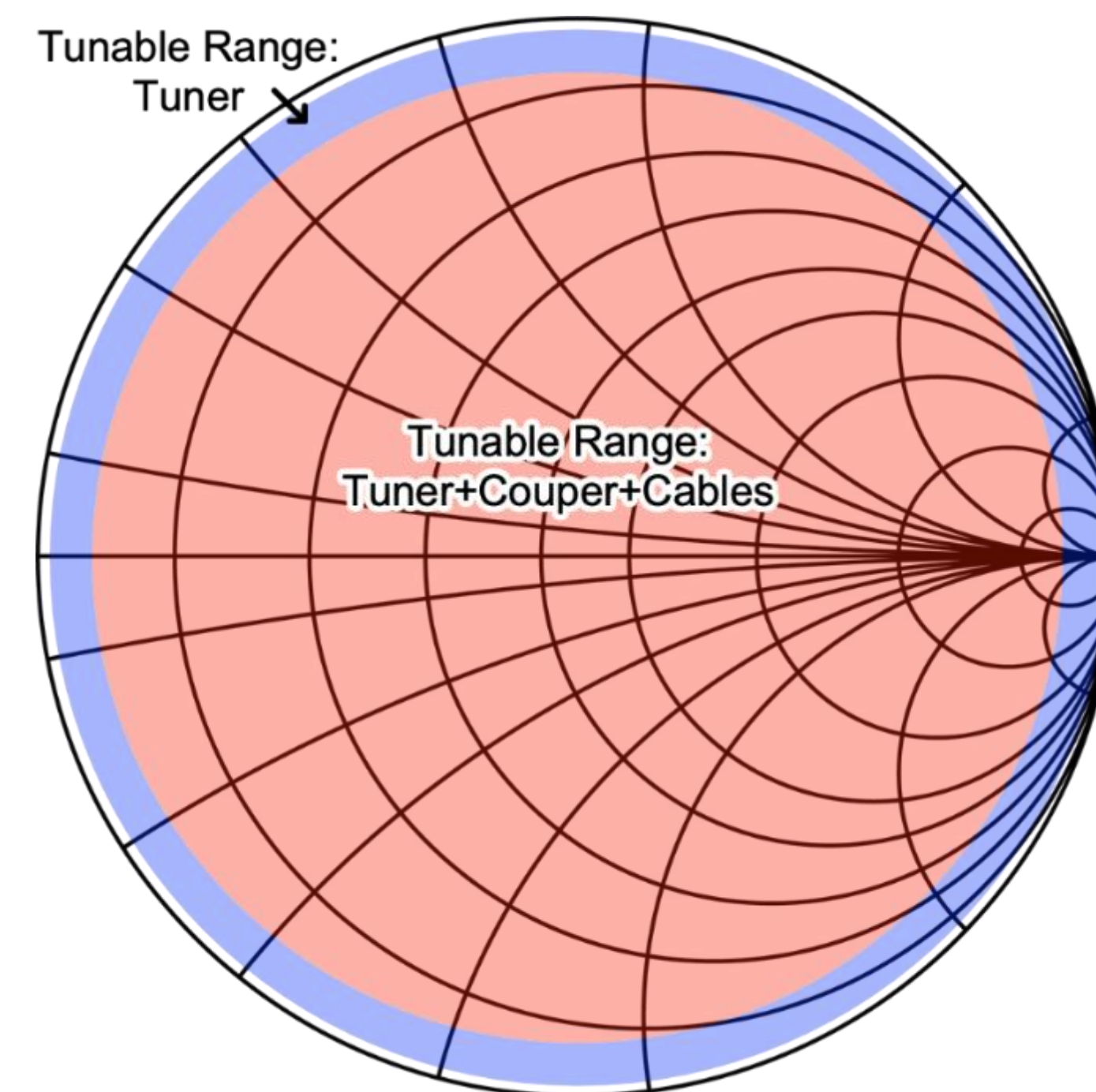
Ref. formulas:

$$RL_{tuner} + RL_{coupler+cable+probe} = RL_{dut}$$

$$RL_{tuner} = -20 \log \left( \frac{VSWR_{tuner} - 1}{VSWR_{tuner} + 1} \right)$$

$$RL_{coupler+cable+probe} = 2(IL_{coupler+cable+probe})$$

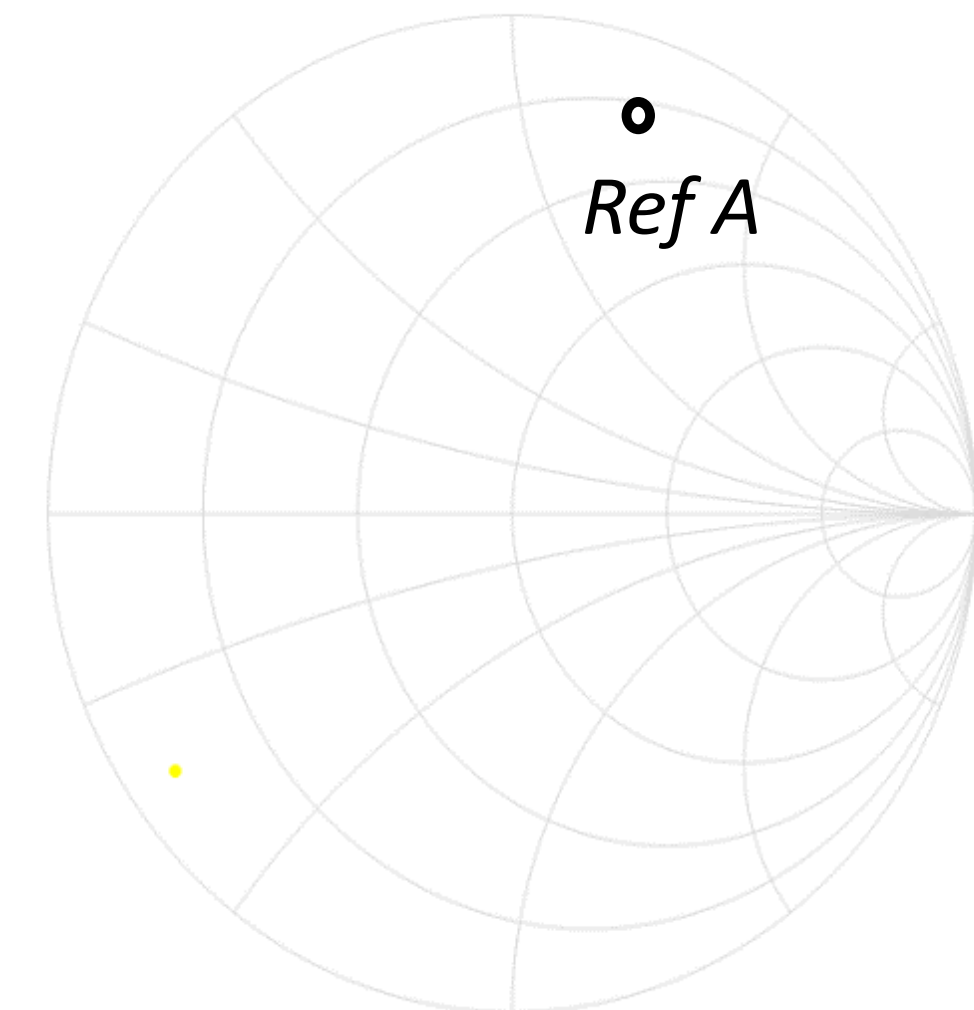
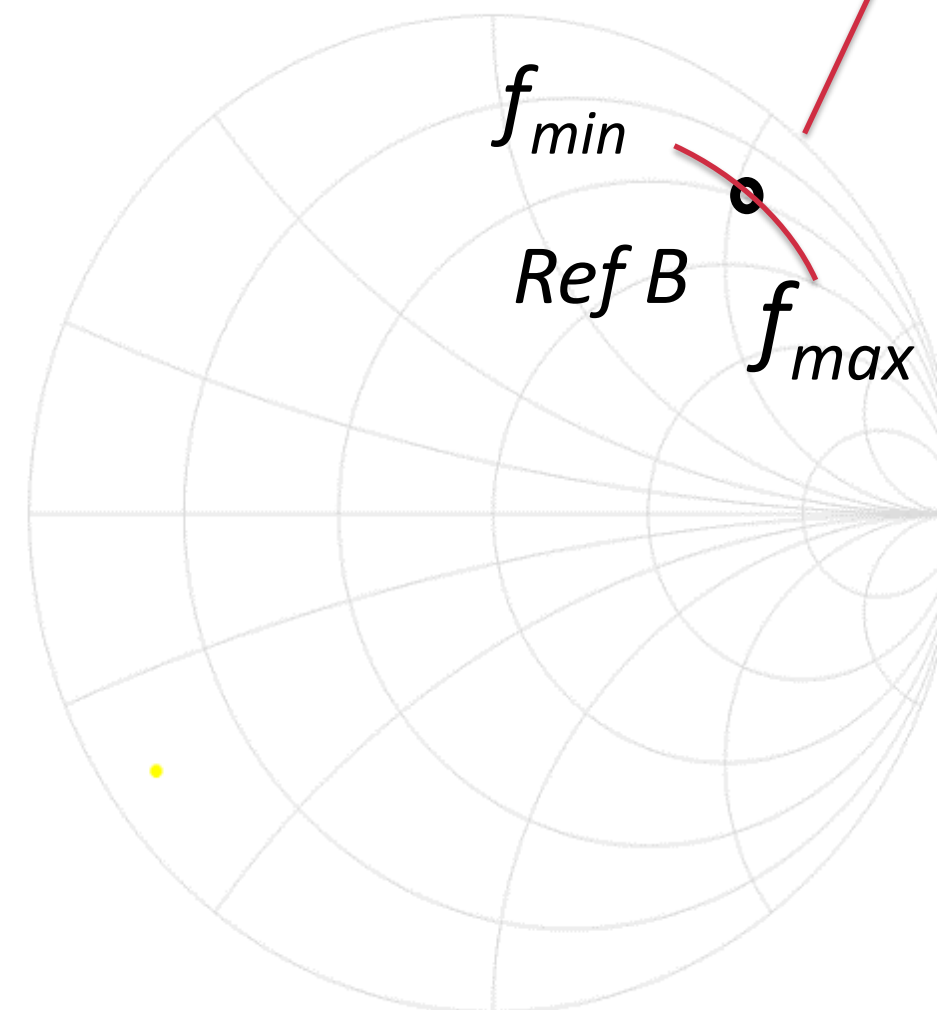
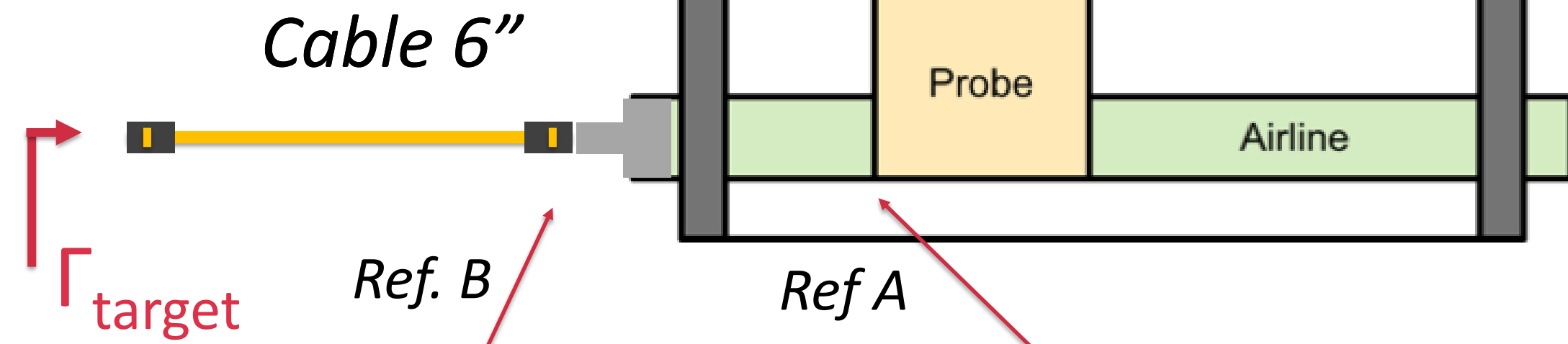
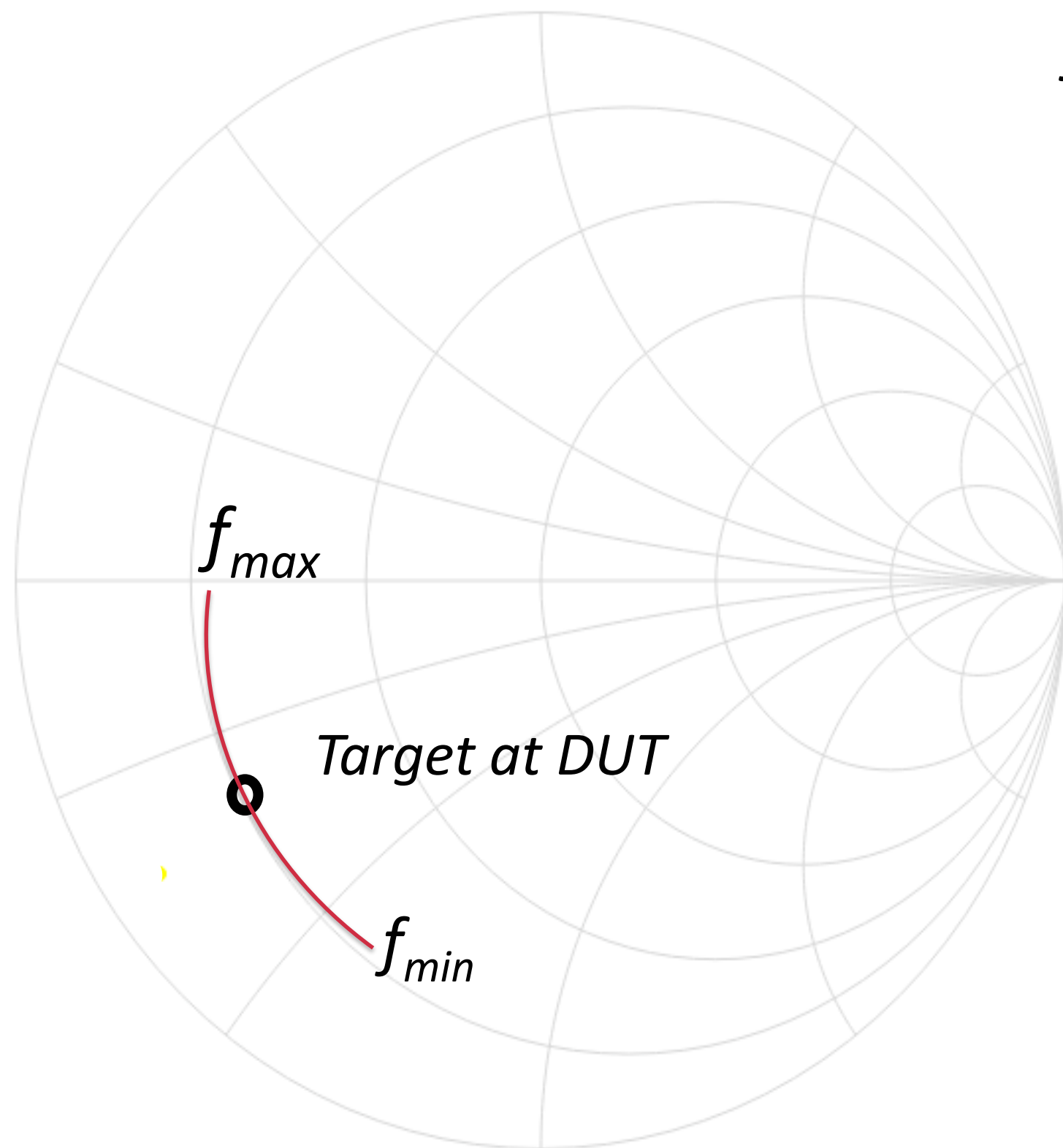
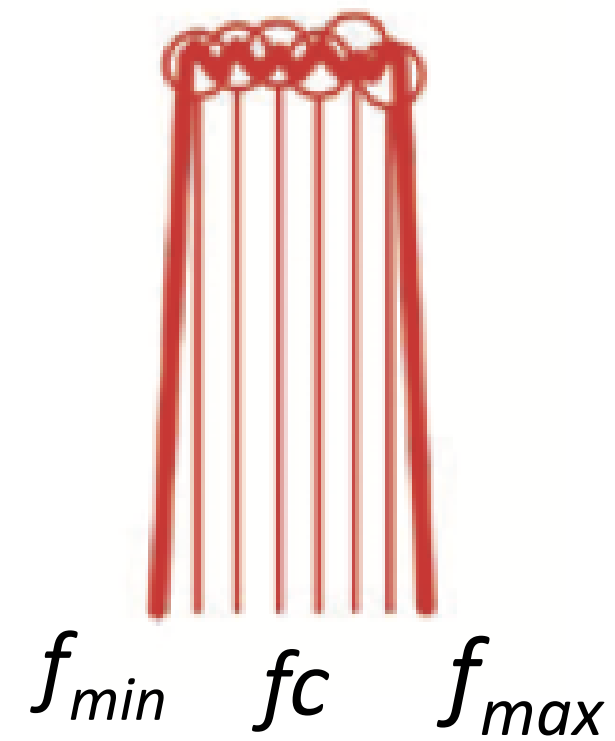
$$\Gamma_{dut} = 10^{\left(\frac{-RL_{dut}}{20}\right)}$$



# Phase skew

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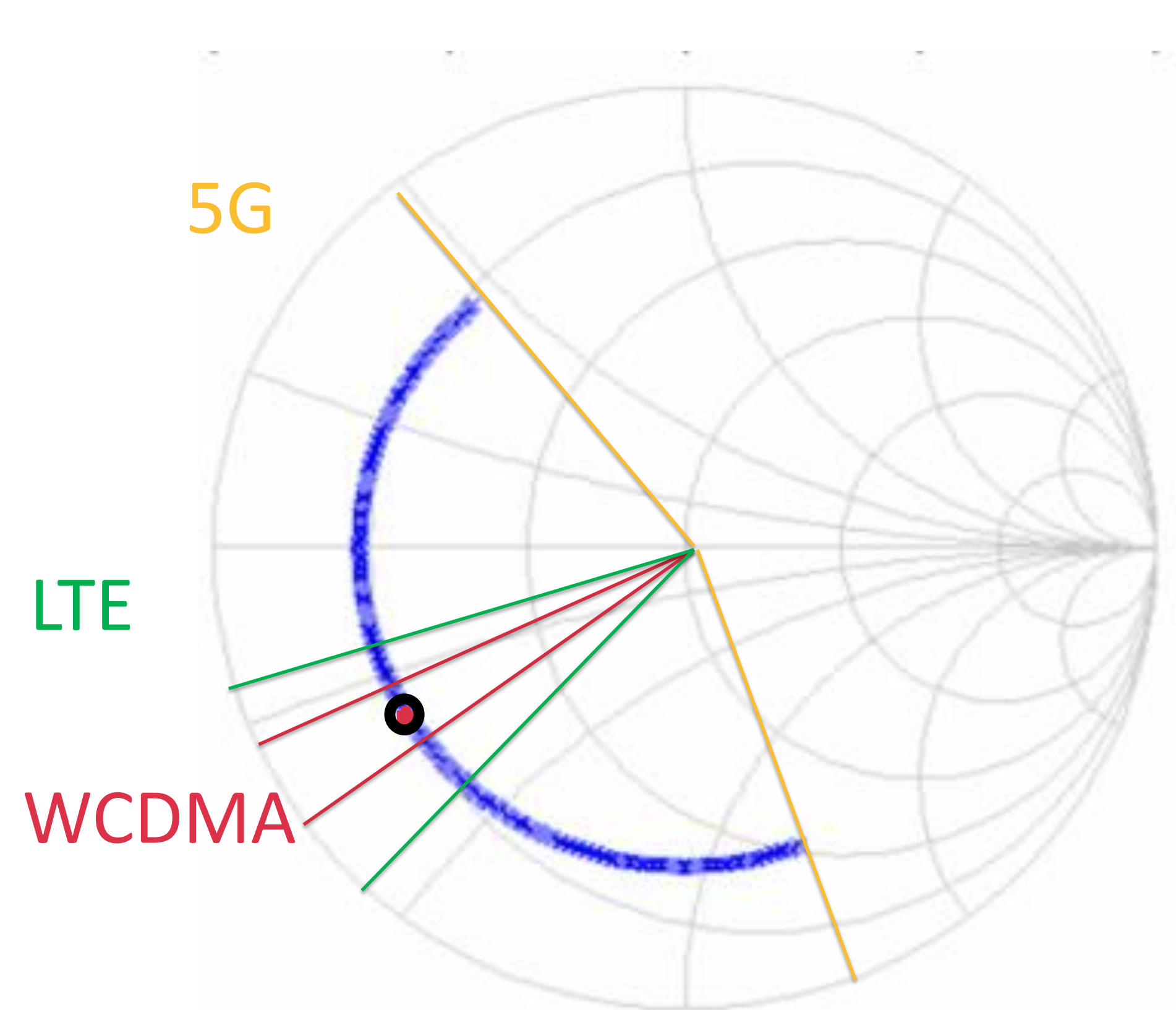
Modulated signal





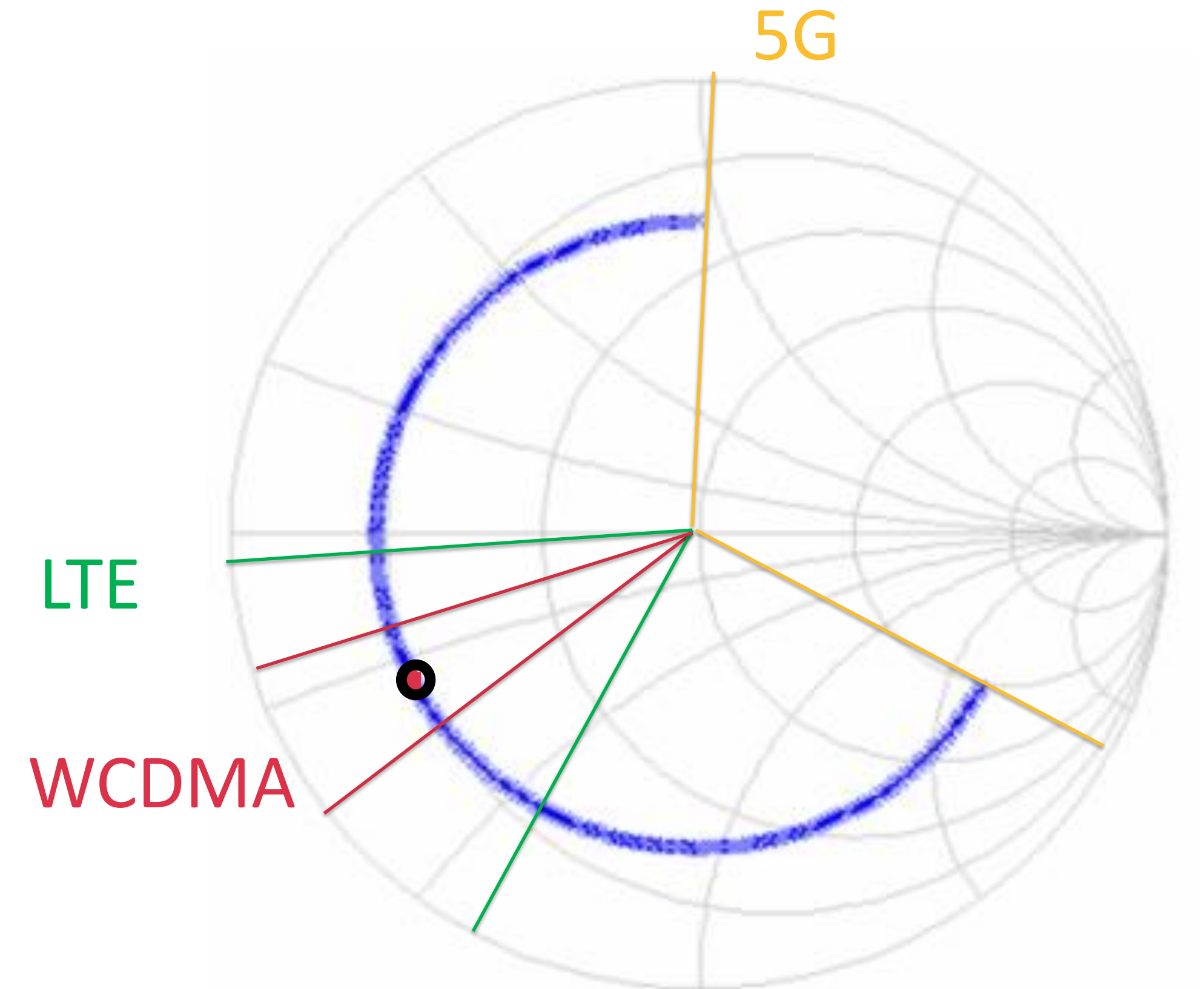
# Phase skew

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Tuner ref

● target



Tuner + short trace line

# ●●●● FR2 and Nano5G

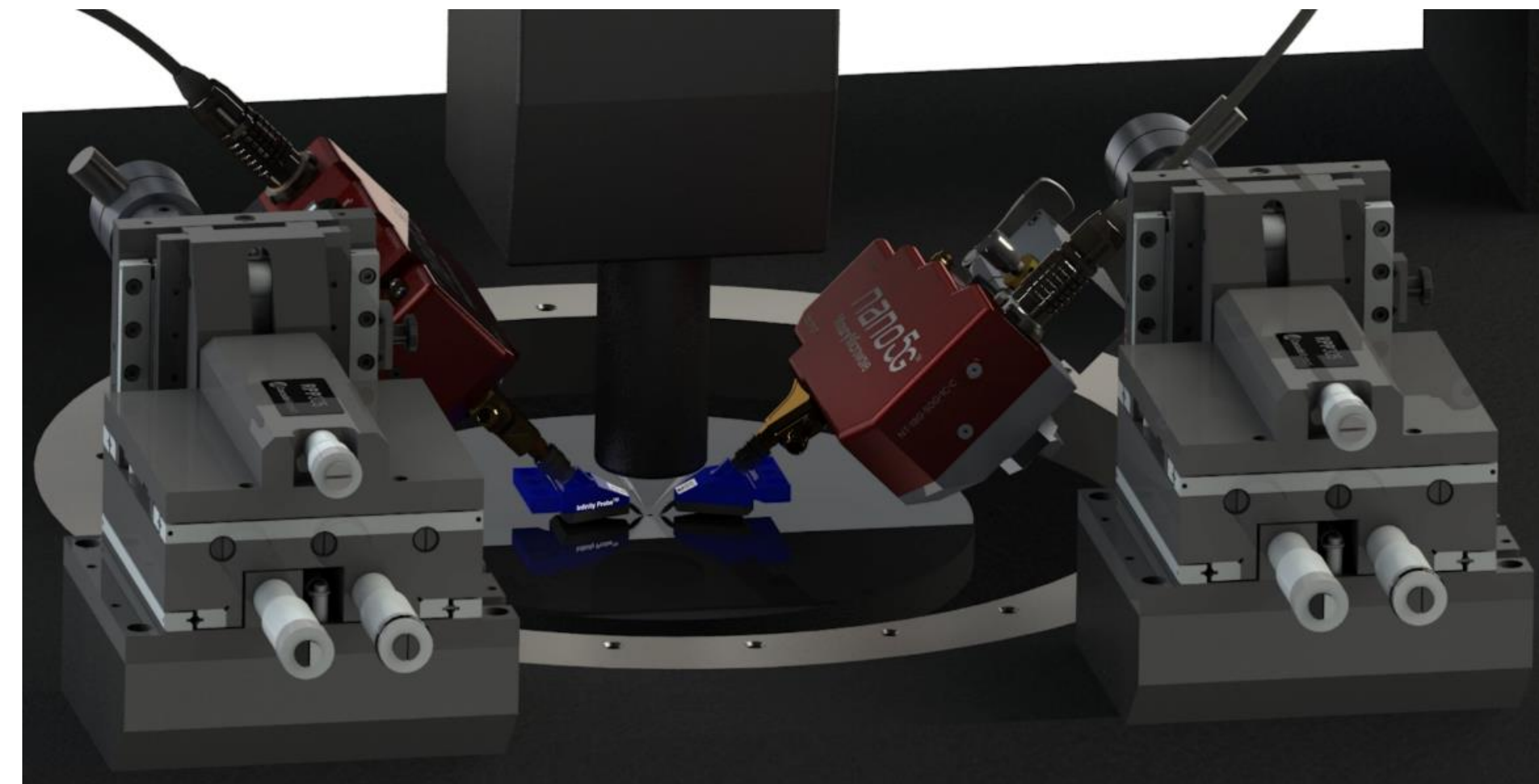
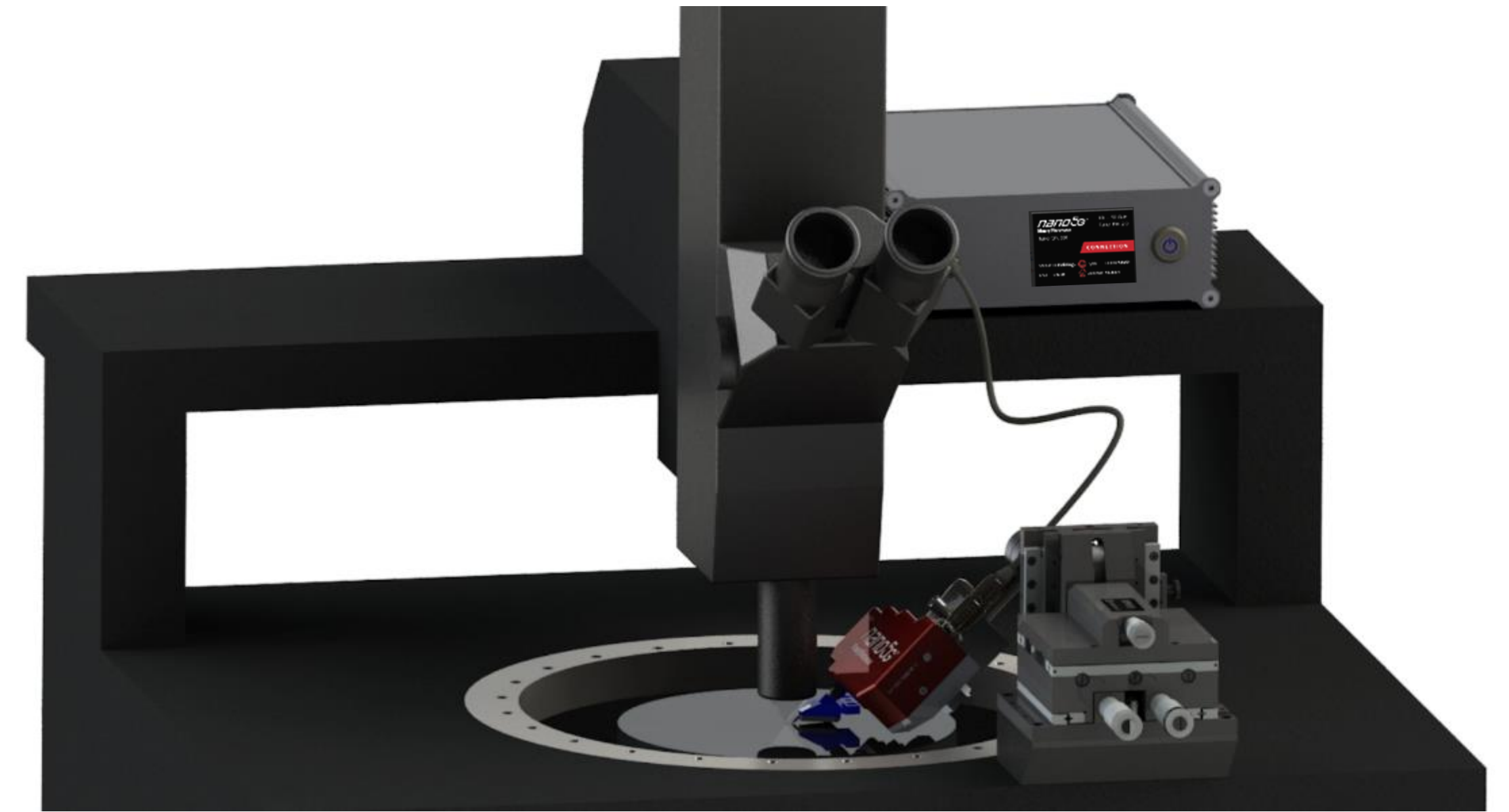
## Challenges:

- Tuning range
- Phase skew
- Speed and accuracy
- Easy SW integration

Maury is introducing at IMS2021 **Nano5G**, 18 GHz-50 GHz tuner directly mounted to probe:

## Nano5G:

- 1/10 of the volume and weight of other solutions:
  - Weight: 0.7 lbs
  - Dimensions: 2.35" x 1.57" x 4.5"
- No cable needed between probe and tuner
- Integrated coupler (optional)



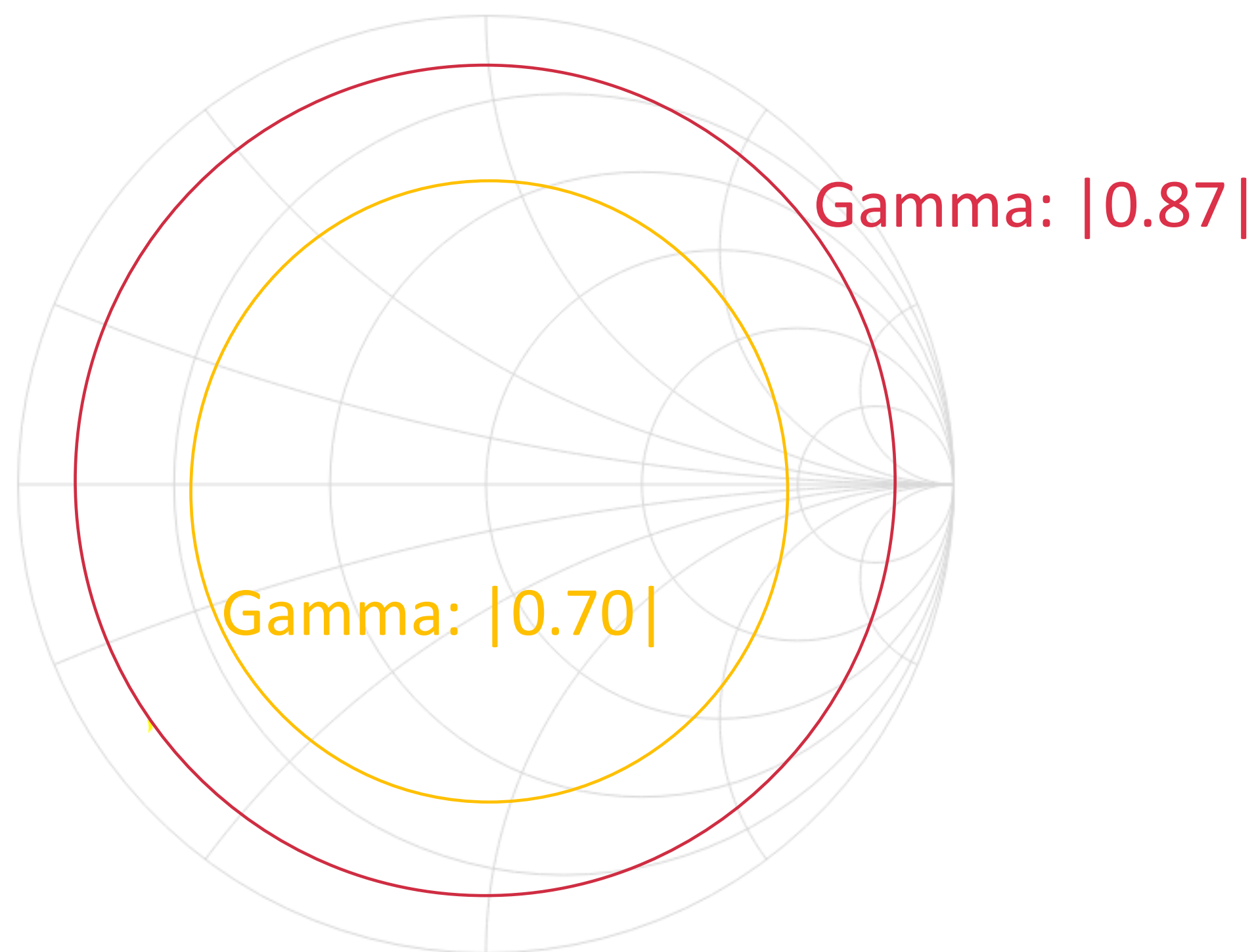


# Features and benefits

Frequency

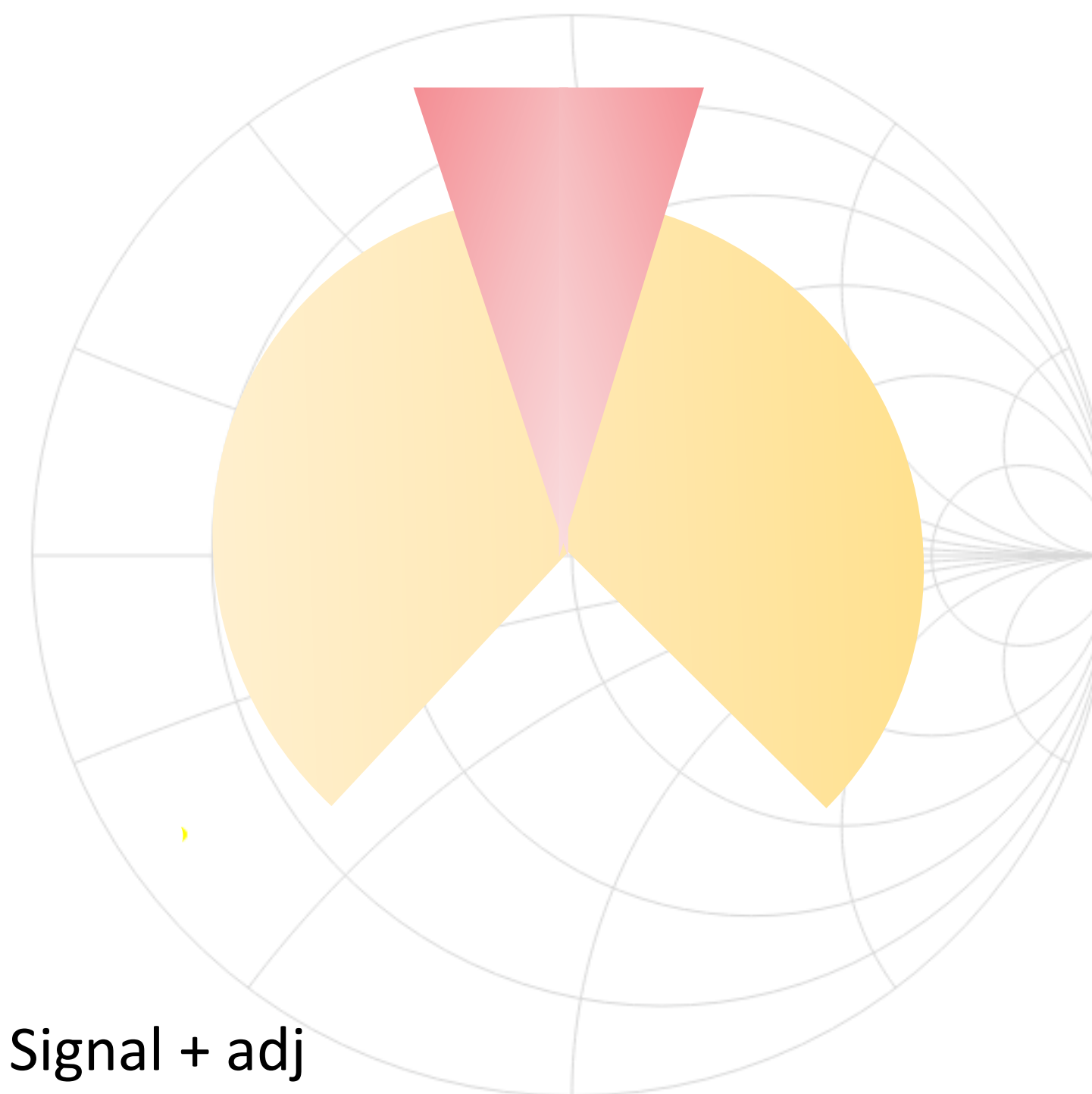
28 GHz

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## Tuning range

(MT984AL01 + coupler with integration cable + probe vs Nano5G + probe)



100MHz Signal + adj  
channels ( left and right)

## Phase skew

(MT984AL01 + coupler with integration cable + probe vs Nano5G + probe)

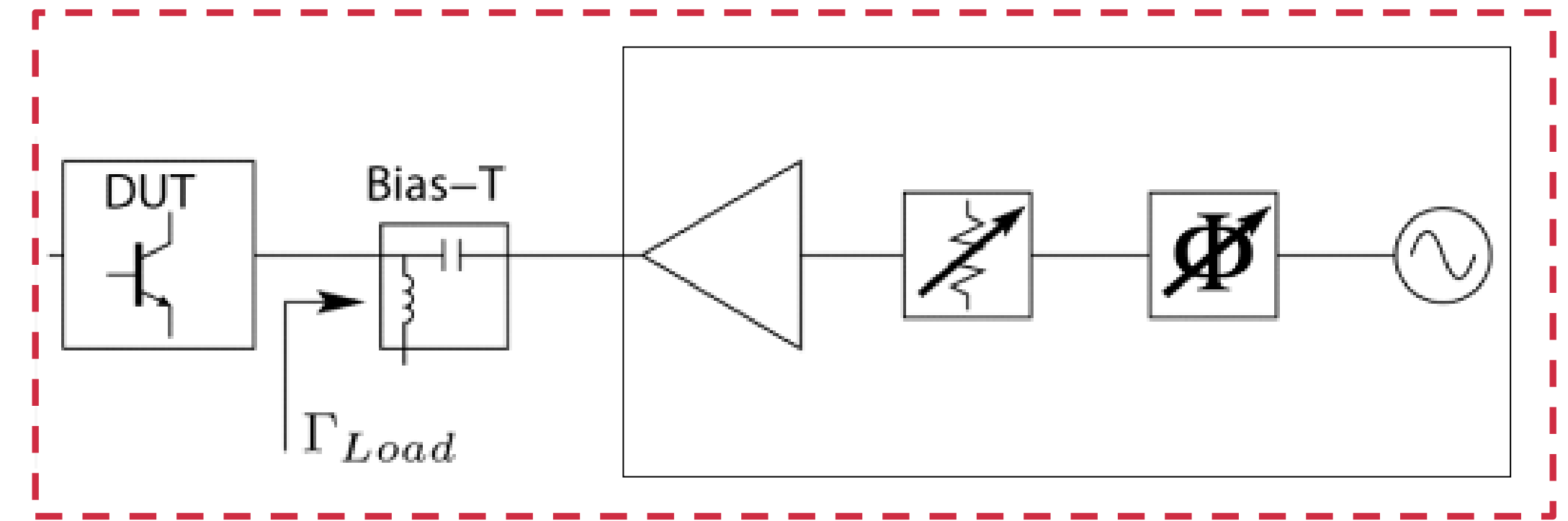
# Active tuning



# ●●●● Active load pull

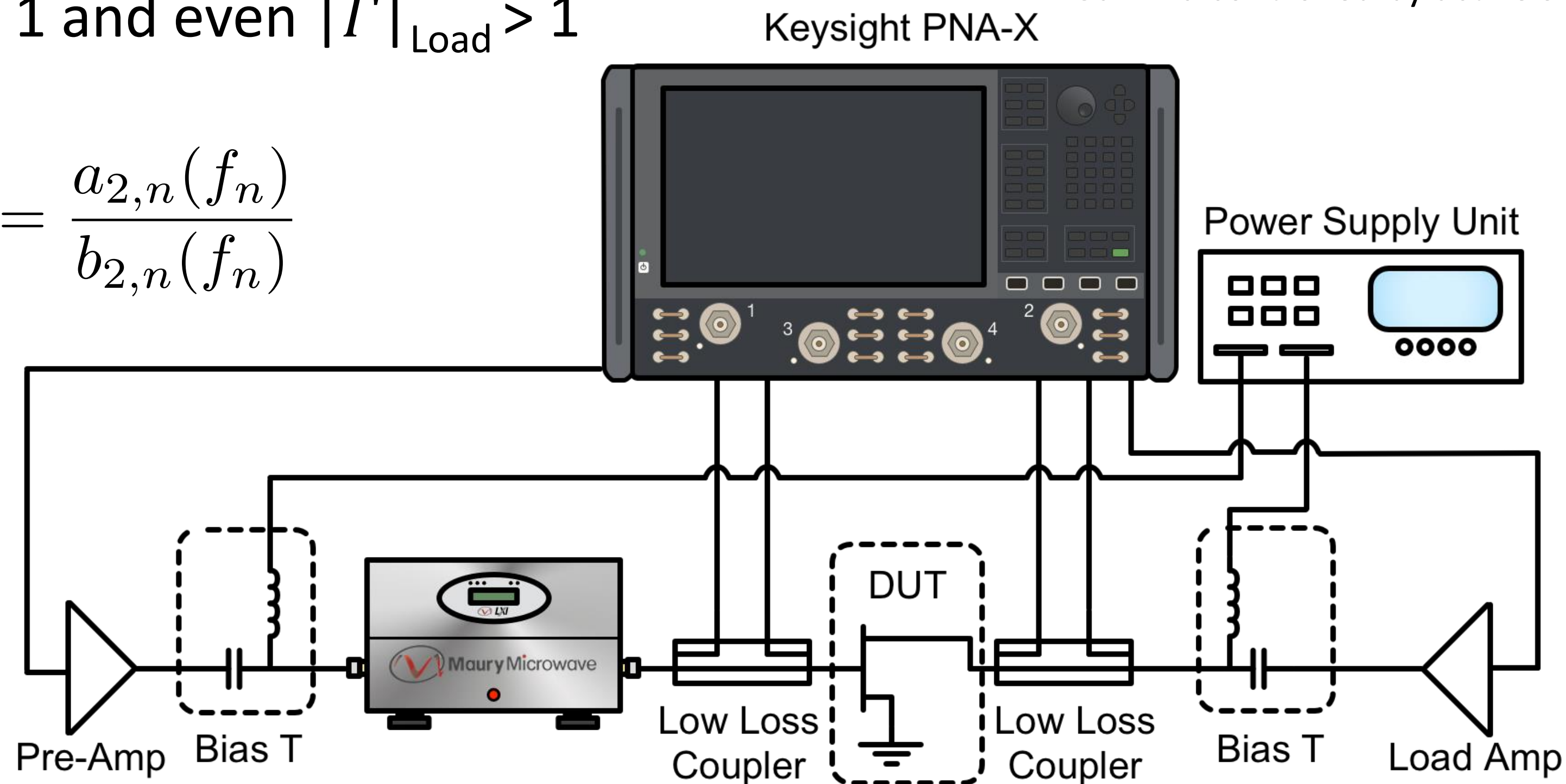
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- Active signal injection used for impedance control
- Measures vector incident and reflected ( $a_x$  and  $b_x$ ) waves
- Measurements performed at calibrated DUT reference plane
- Enables  $|\Gamma|_{\text{Load}} = 1$  and even  $|\Gamma|_{\text{Load}} > 1$

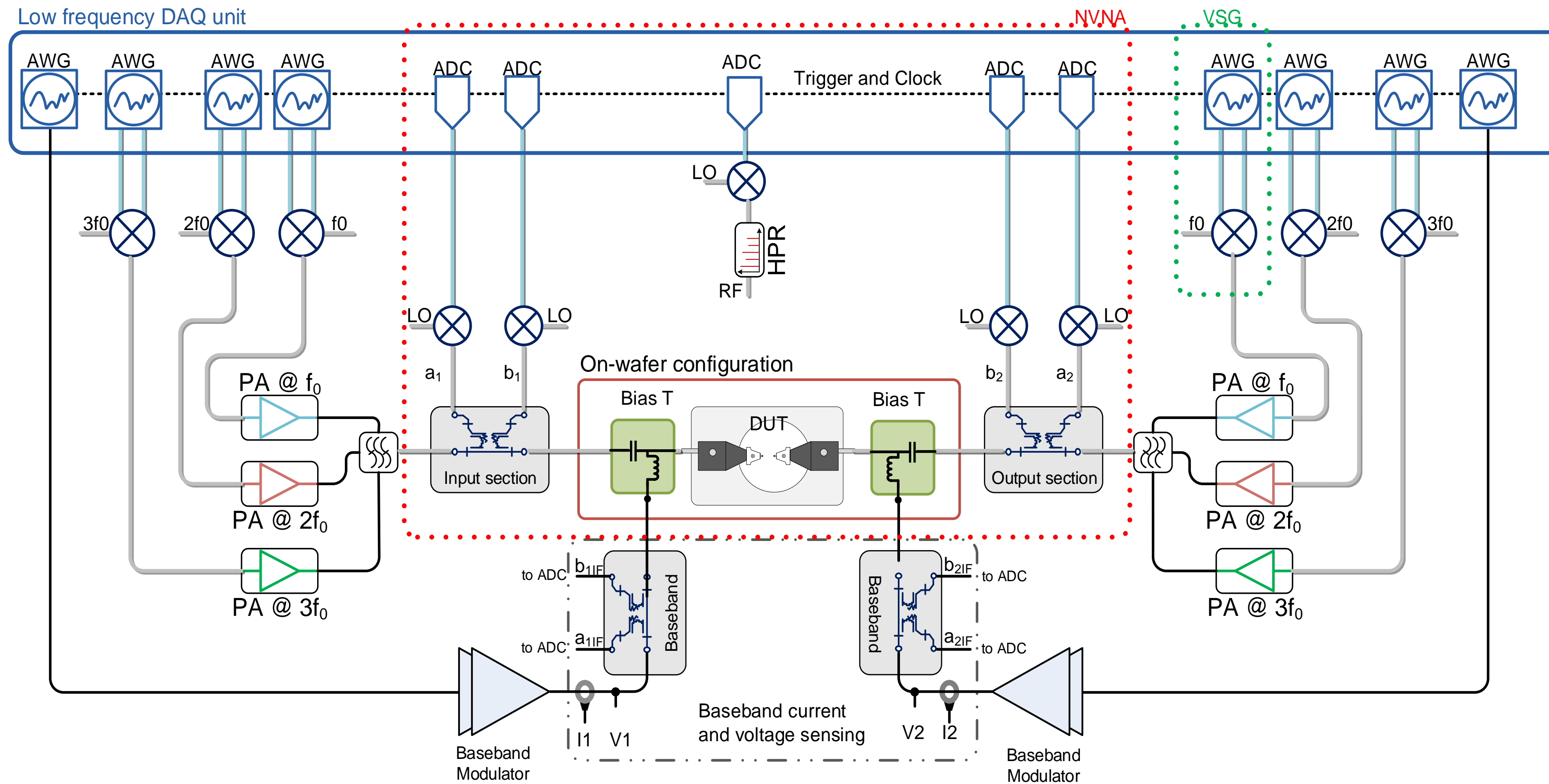


Gamma controlled by active signal injection

$$\Gamma_{\text{Load},n}(f_n) = \frac{a_{2,n}(f_n)}{b_{2,n}(f_n)}$$

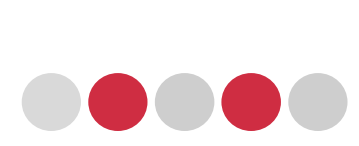


# MT2000 mixed-signal vector load-pull for modulated signal characterization

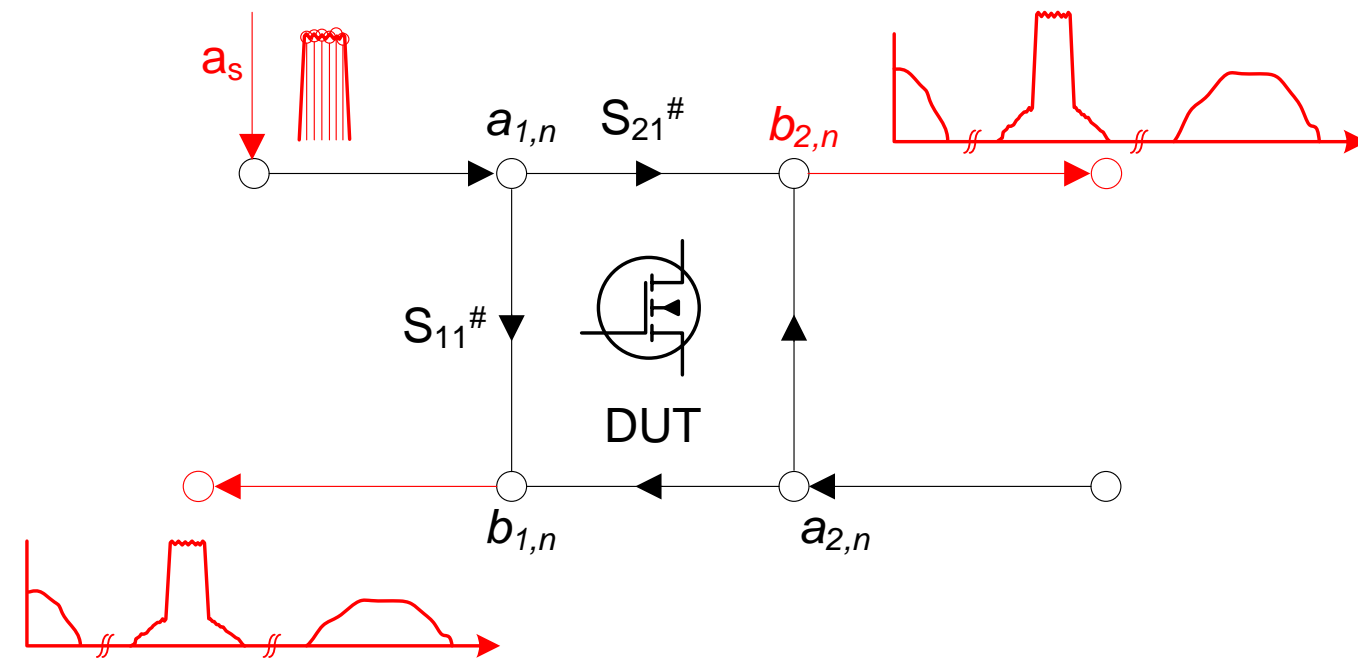


- (N)VNA-like receiver architecture without narrowband filtering in order to allow wideband modulation acquisition
- Multiple vector signal generators (AWGs) are used as active tuners

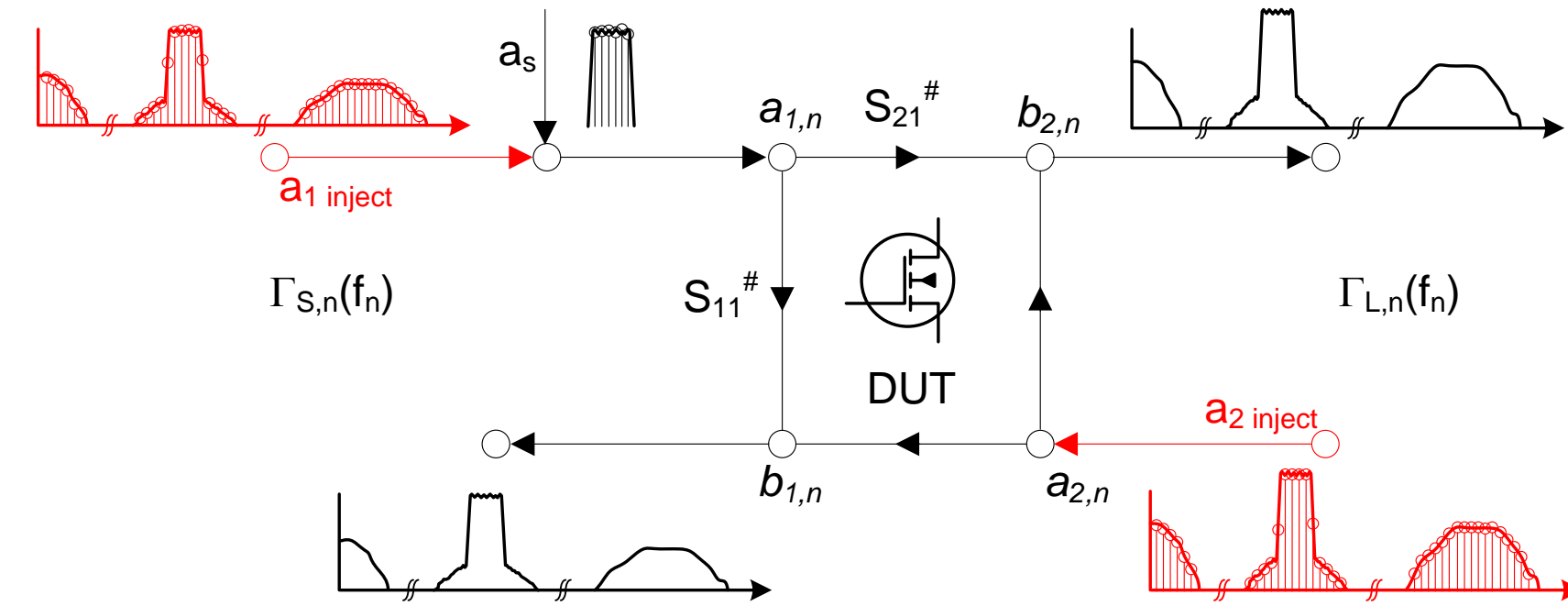




# Wideband Load Pull Algorithm



Step 1: A non-linear device excited with a modulated signal will emanate waves (b-waves) at the harmonic and baseband frequencies



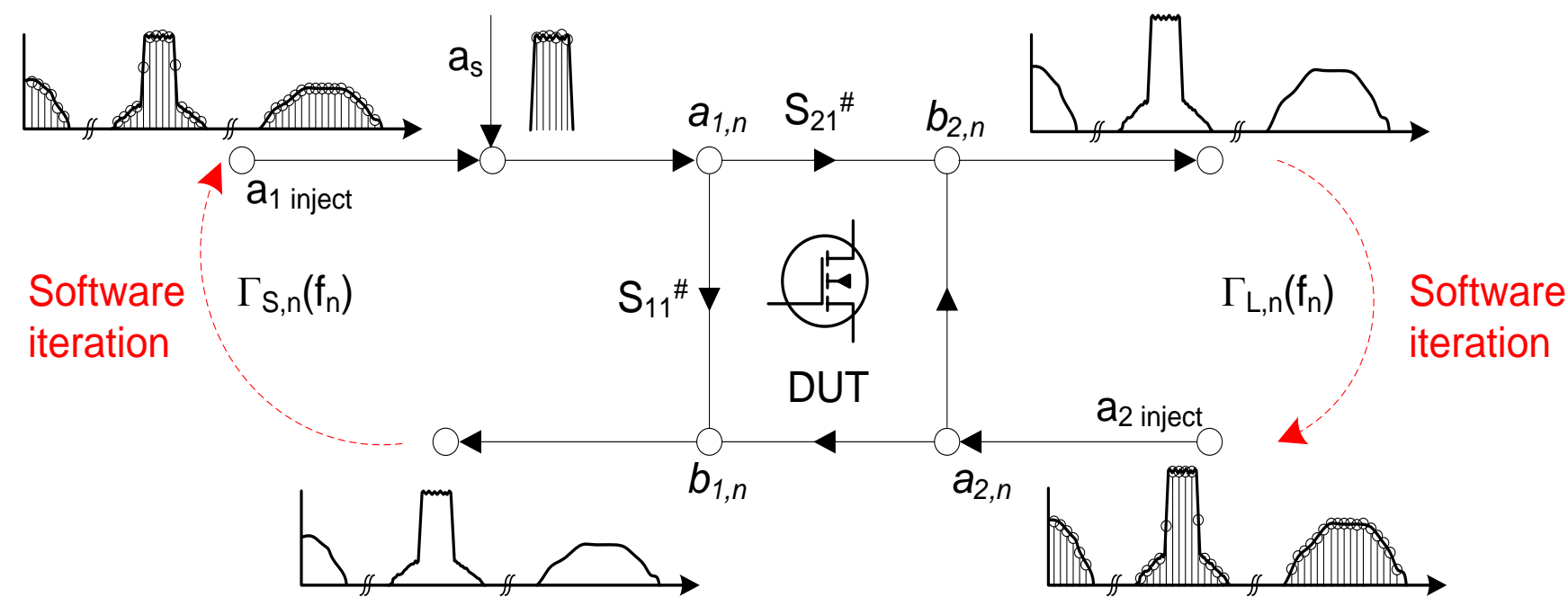
Step 2: By measuring the  $\Gamma$  at the DUT, the a-waves to be injected to obtain a user-specified reflection coefficient can be estimated.

$$\Gamma_{x,n}(f_n) = \frac{a_{x,n}(f_n)}{b_{x,n}(f_n)}$$

$x$  = source ( $s$ ) or load ( $l$ )

$n$  = frequency band, e.g. baseband (0), fundamental (1) and harmonic (2 and up)

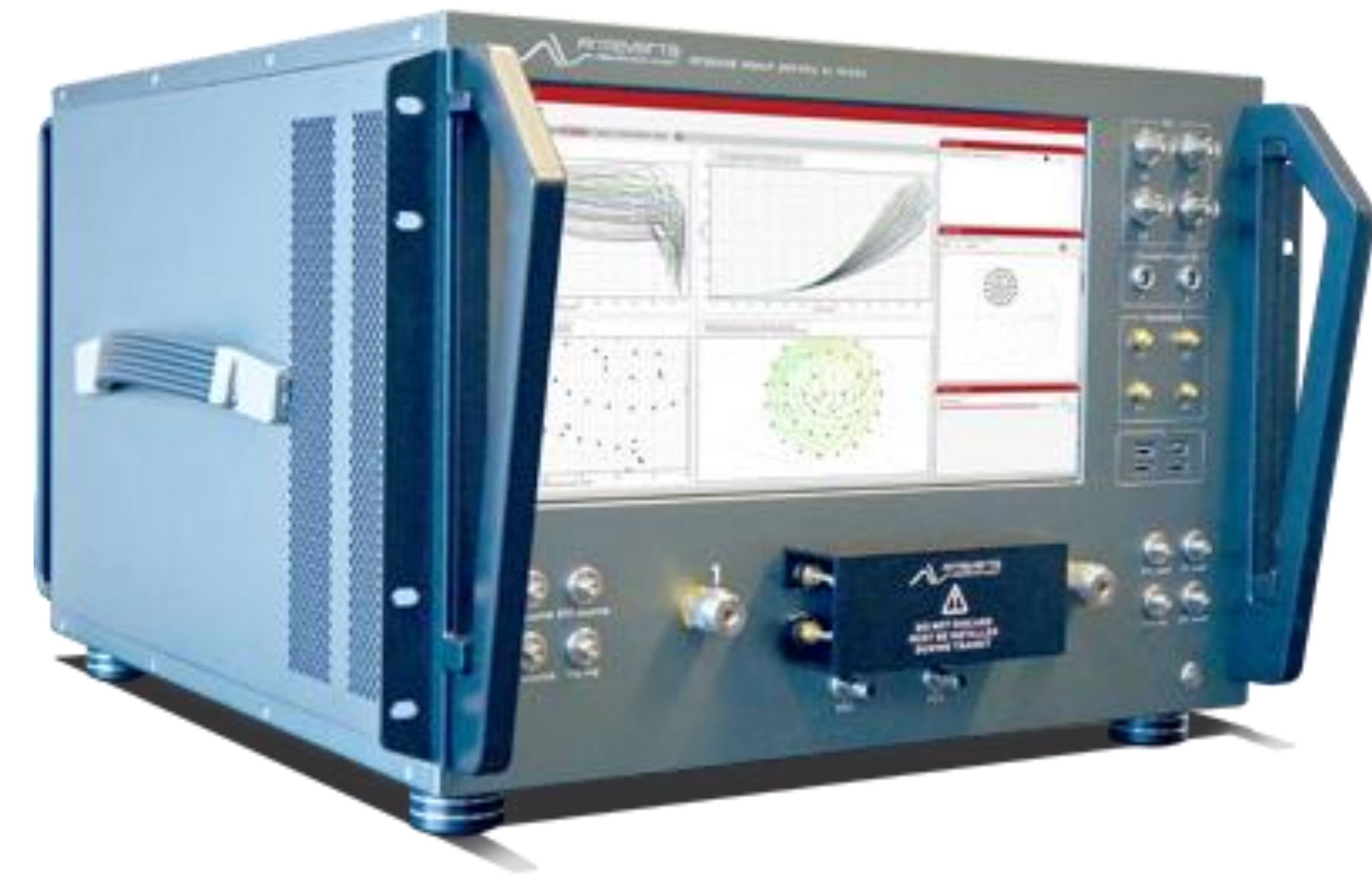
$\Gamma_{\text{frequency}}(f_n)$  = user defined reflection coefficient vs. frequency



Step 3: Software iteration based on the reflection coefficient measurements at the DUT reference planes

# ●●●● Key features

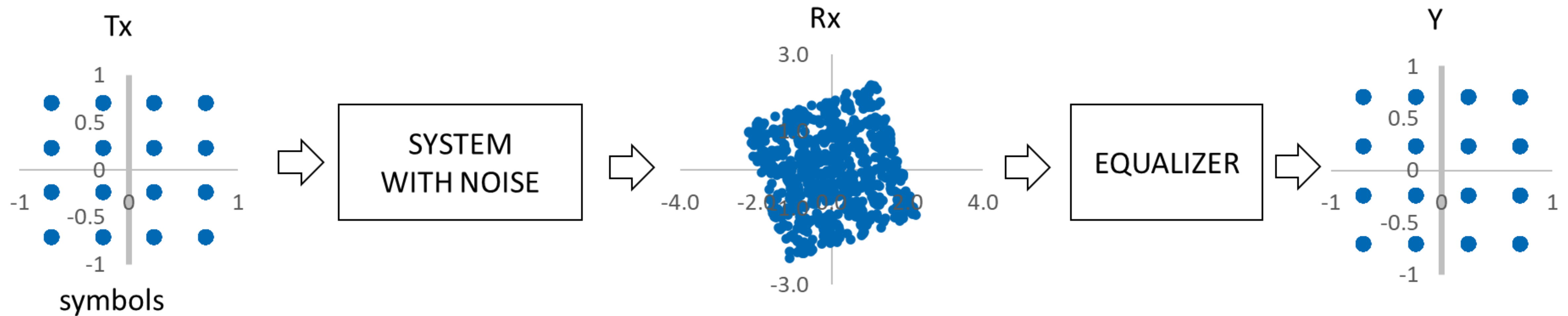
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- Traditional analog and microwave techniques with low-frequency signal acquisition (A/D converters) and generation (Wideband AWG);
- Ultra fast CW and pulsed CW load pull
- Wideband ADCs allow measurement of wideband signals (power, ACPR, EVM)
- Frequency scalable: currently up to **67 GHz**
- System includes **6 VSGs** to generate custom modulations up to **1000 MHz** bandwidth
- Each VSG can be used as an active tuner
- VNA + NVNA + Oscilloscope + Signal Analyzer + Behavioral Model extraction in one solution

# ●●●● EVM measurements - background

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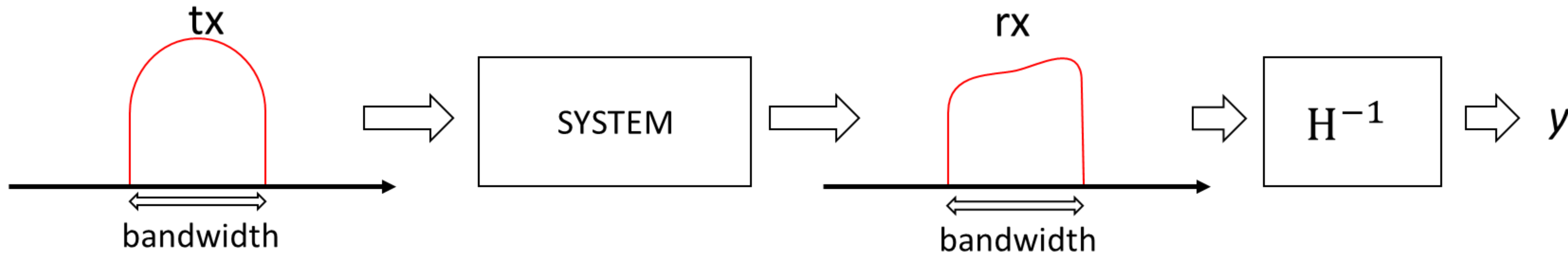
- linear and nonlinear distortion;
- thermal noise;
- ISI;

$$EVM = \sqrt{\frac{\sum |Y - T_x|^2}{\sum |T_x|^2}}$$



# Generalized EVM measurement method

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$$R_x(f) = H(f)T_x(f) + D(f)$$

$$rx = h \otimes tx + d$$

$d$  is the uncorrelated distortion

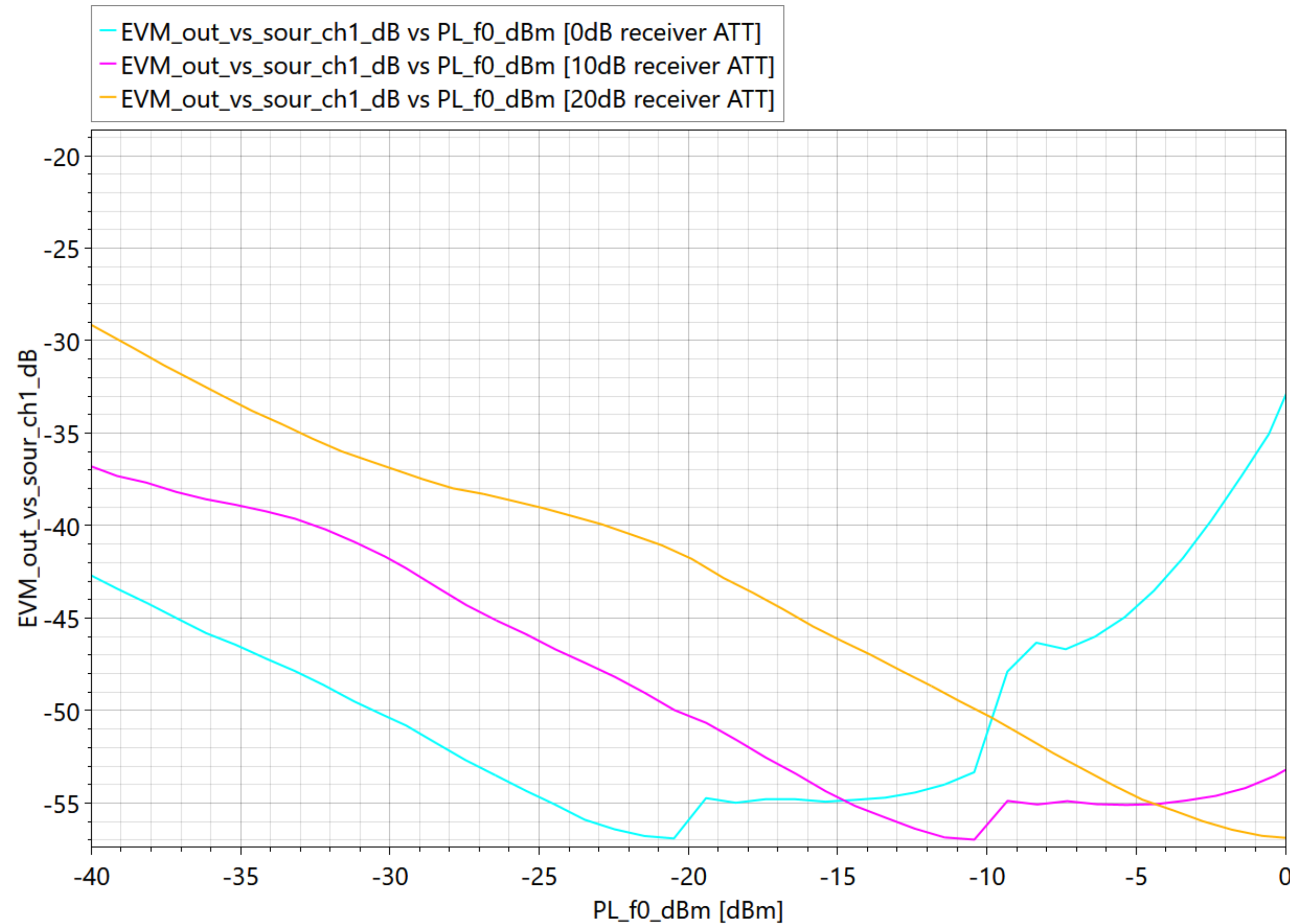
$$EVM = \sqrt{\frac{\sum |y - tx|^2}{\sum |tx|^2}} = \sqrt{\frac{\sum |h^{-1} \otimes rx - tx|^2}{\sum |tx|^2}} \Rightarrow \text{Estimation of filter}_{1,2} h$$

<sup>1</sup>Linear Approximations of Nonlinear FIR Systems for Separable Input Processes, *Martin Enqvist, Lennart Ljung, 2005*

<sup>2</sup>Measurement Methods for Estimating the Error Vector Magnitude in OFDM Transceivers, *Karl Freiberger, 2017*



# ●●●● EVM measurements: noise floor



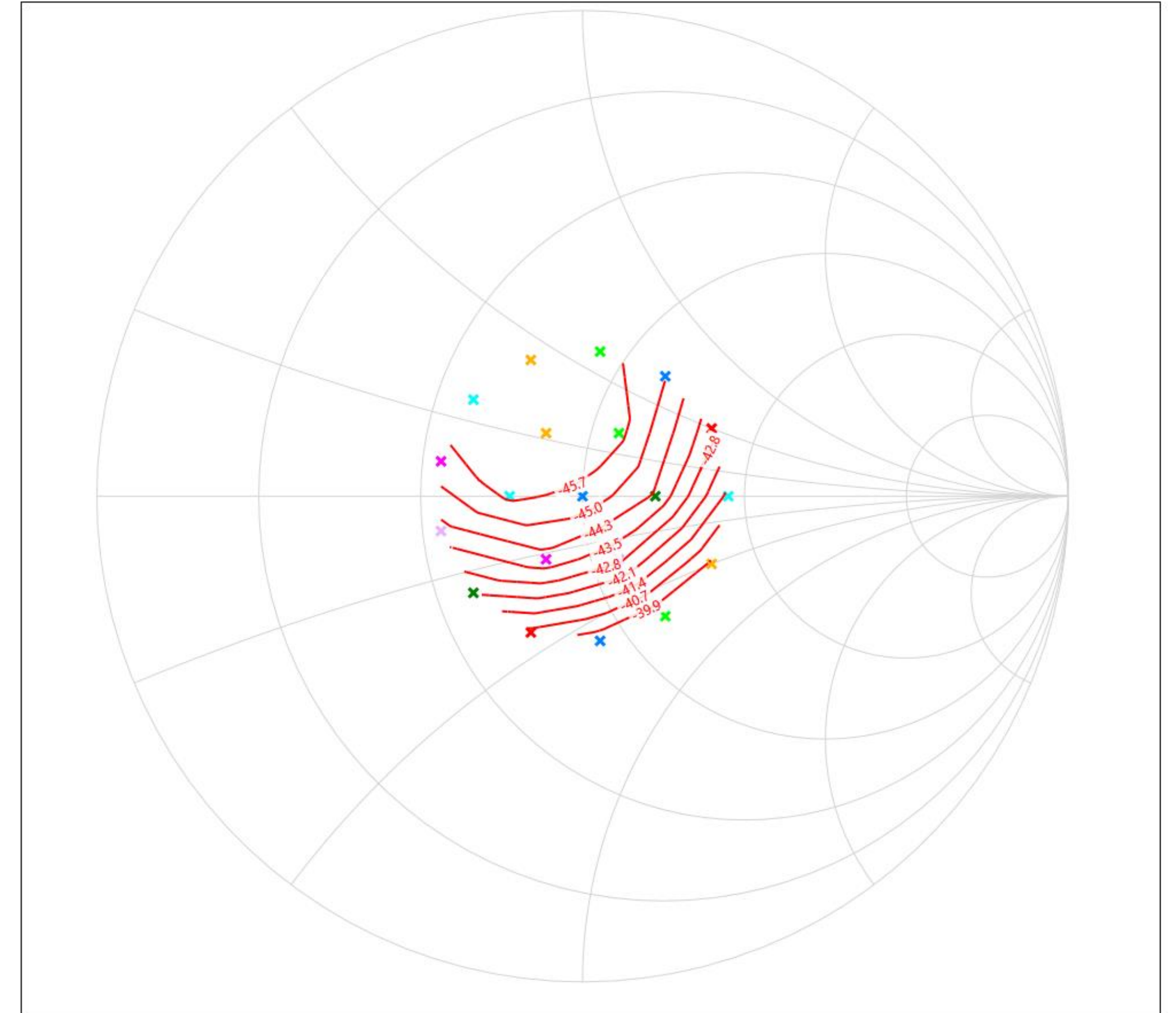
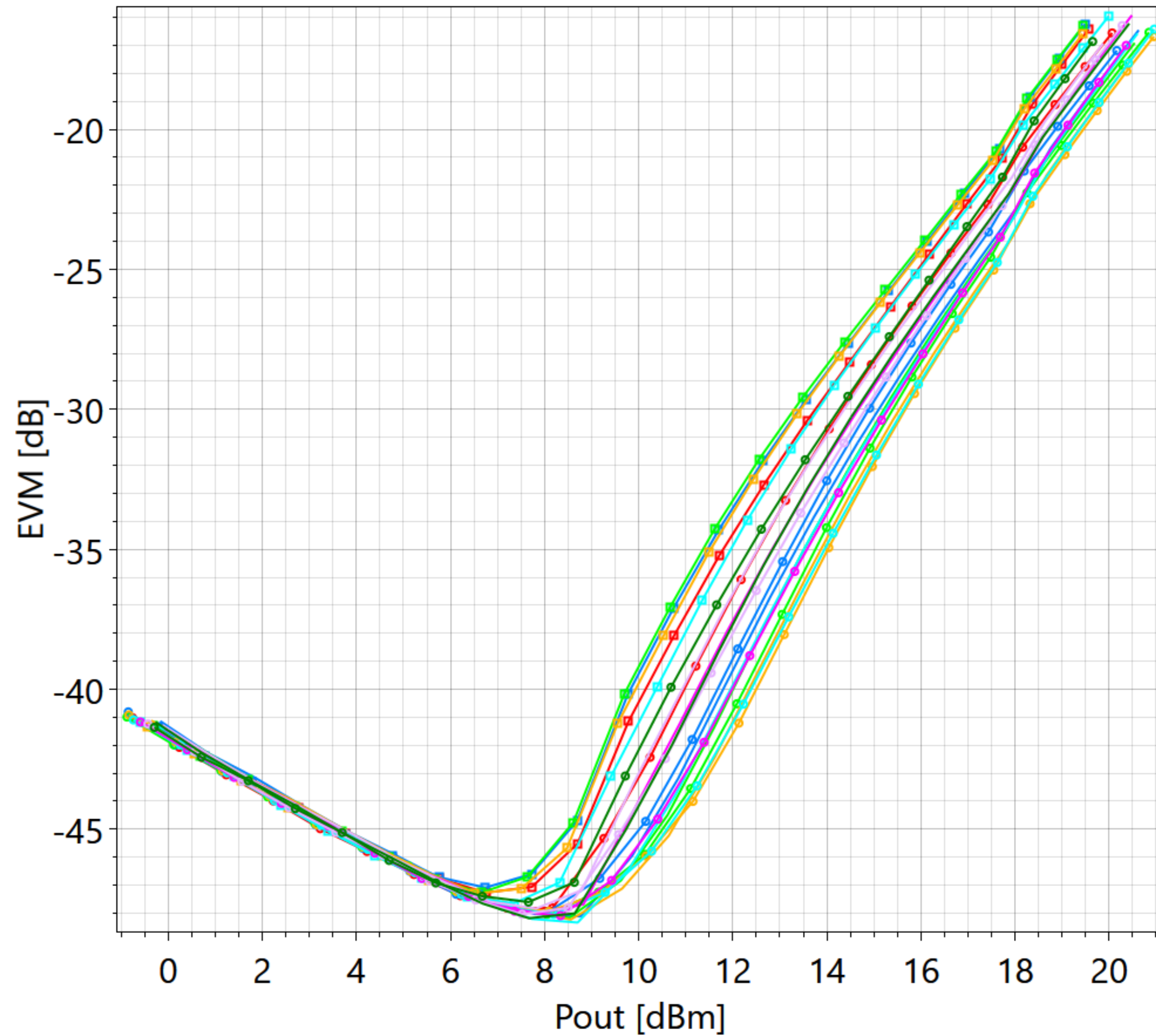
- Signal:  
fr2\_64qam\_100M\_120khz\_cpofdm
- Carrier frequency = 9 GHz

## Comments:

- Receiver stepping automated to optimize noise floor across power sweep

# ●●●● EVM measurements w/ active load pull

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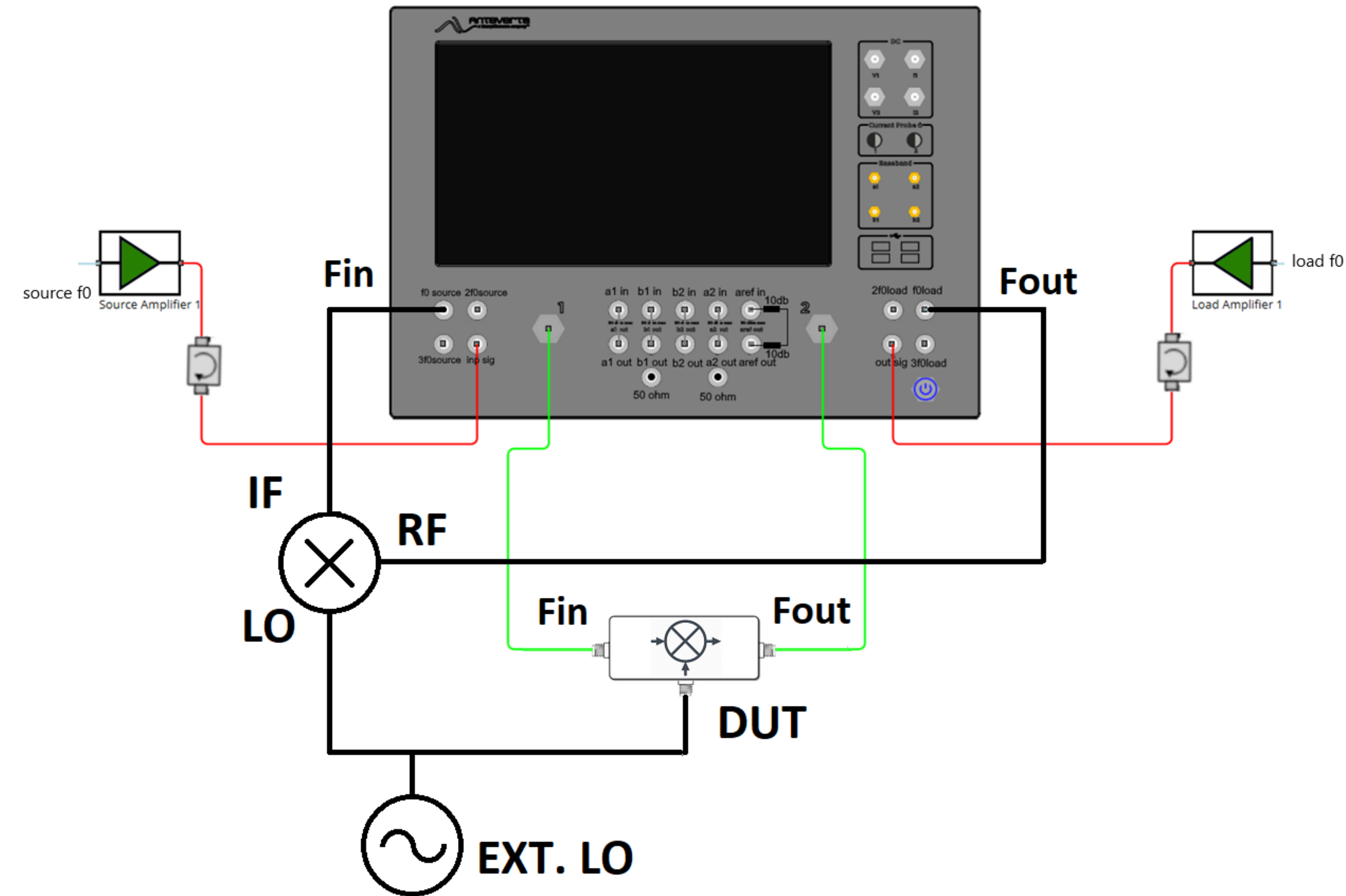
- WLAN 80211ax MCS9 3.5 GHz, BW = 320 MHz
- Measurements on a matched amplifier module





# Load-pull on upconverters

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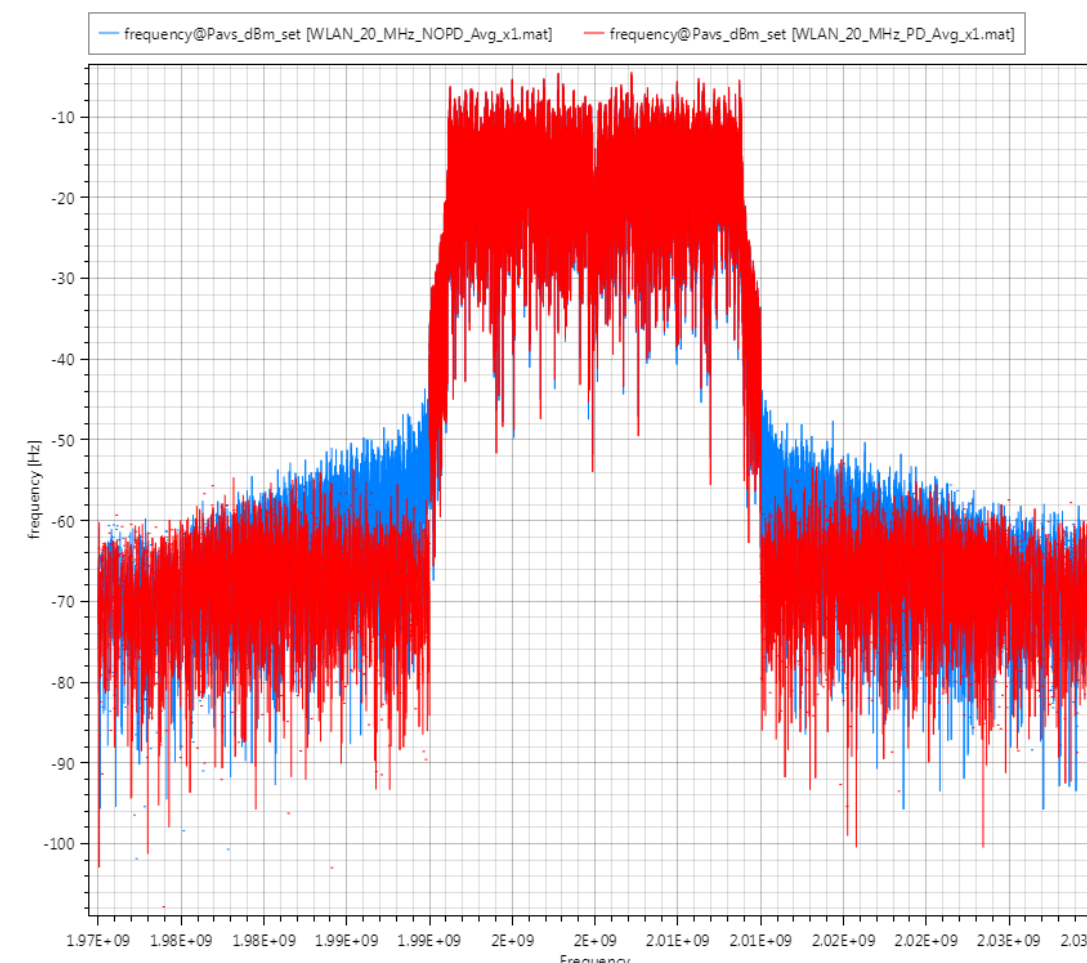
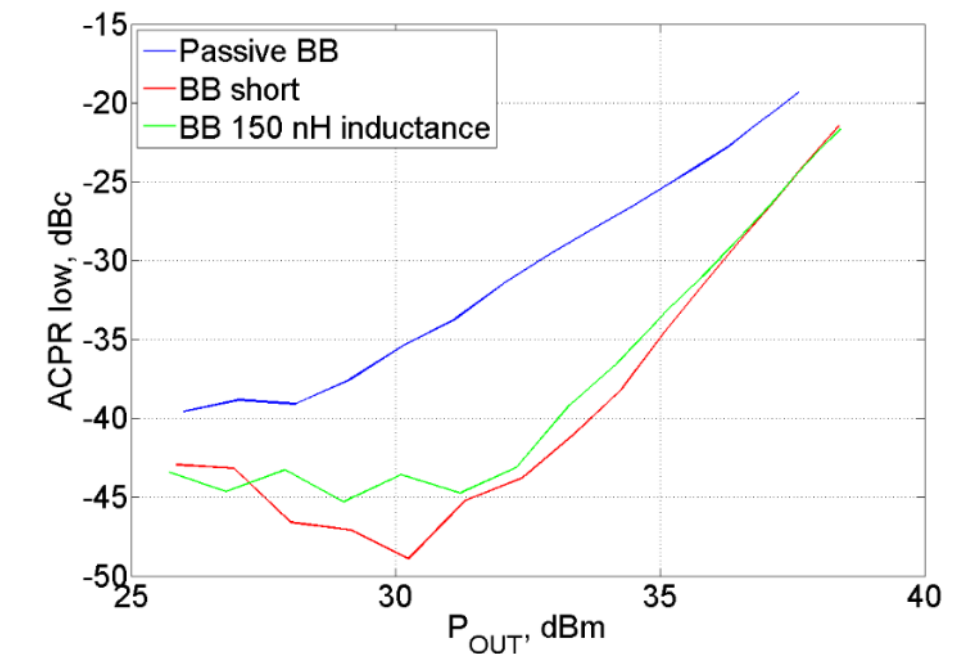
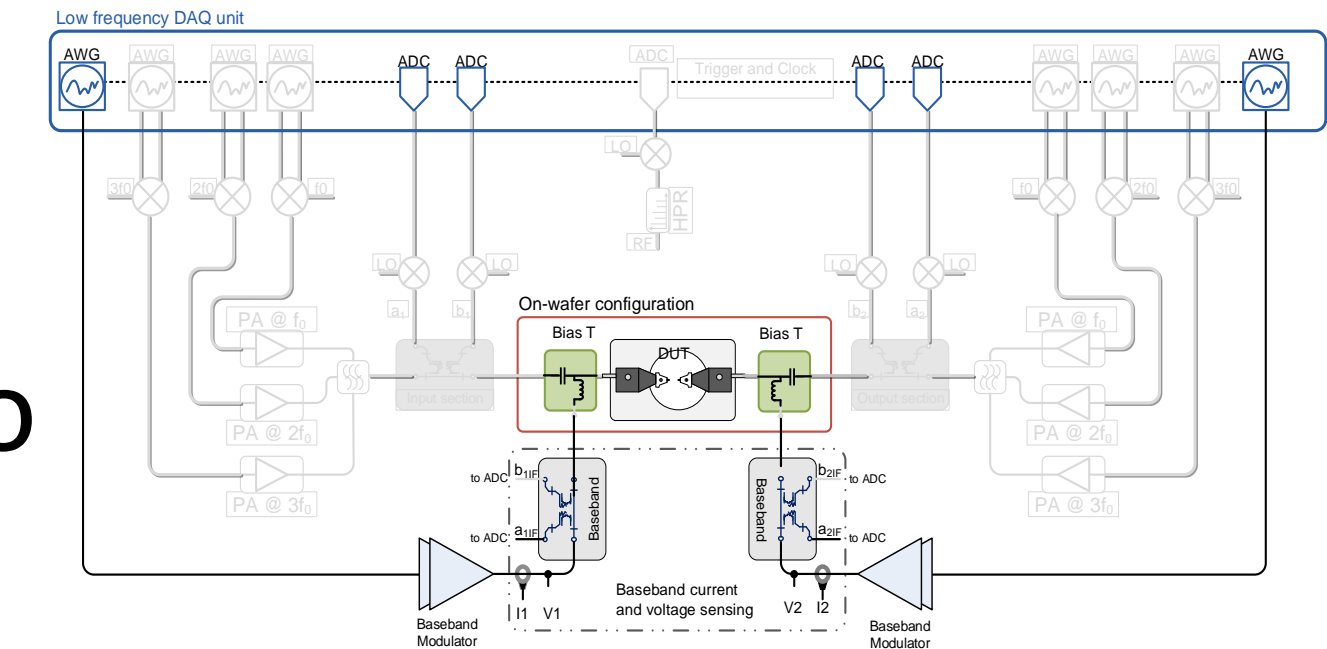
- An external LO is used by the DUT for the up-conversion from  $F_{in}$  to  $F_{out}$
- The same LO is used with an auxiliary mixer to up-convert the system source signal ( $F_{in}$ ) and generate the signal used for the load impedance control ( $F_{out}$ )



# Additional requirements

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- Baseband impedance control
  - Active load-pull applied to tune baseband impedance to enhance linearity (up to 200 MHz)
- DPD under load-pull conditions (spectral DPD, time-domain DPD)





# mmW and sub-THz waveguide passive, active and hybrid-active vector-receiver load pull

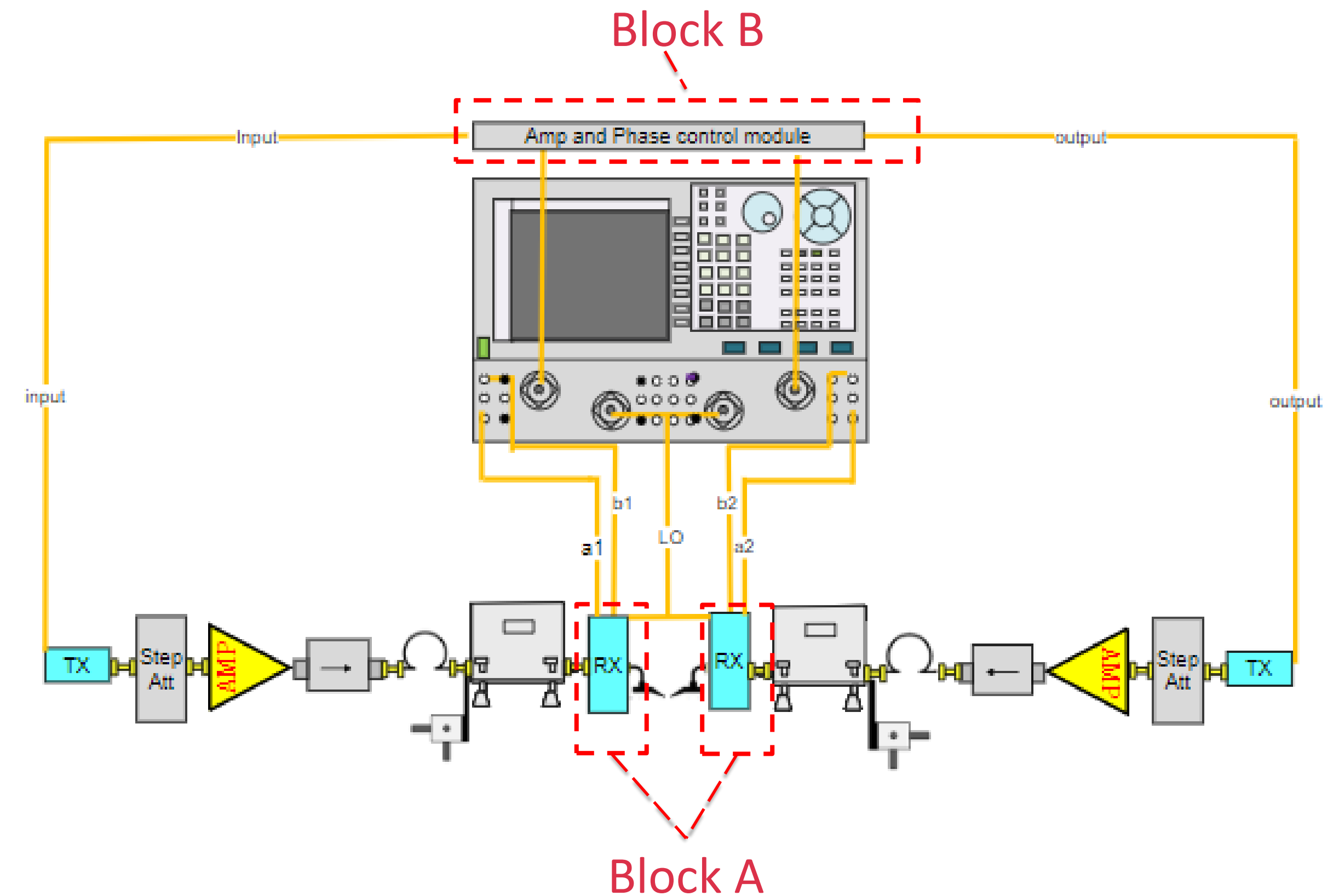


# Waveguide load pull

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## Hardware to empower waveguide passive and hybrid-active load pull

- Low-loss couplers with integrated down-conversion (block A) allows for direct measurement of a- and b-waves
- Input and output amplitude and phase control module before up-conversion (block B) allows for high-resolution control of injected active tuning signal





# Waveguide passive and hybrid-active LP system

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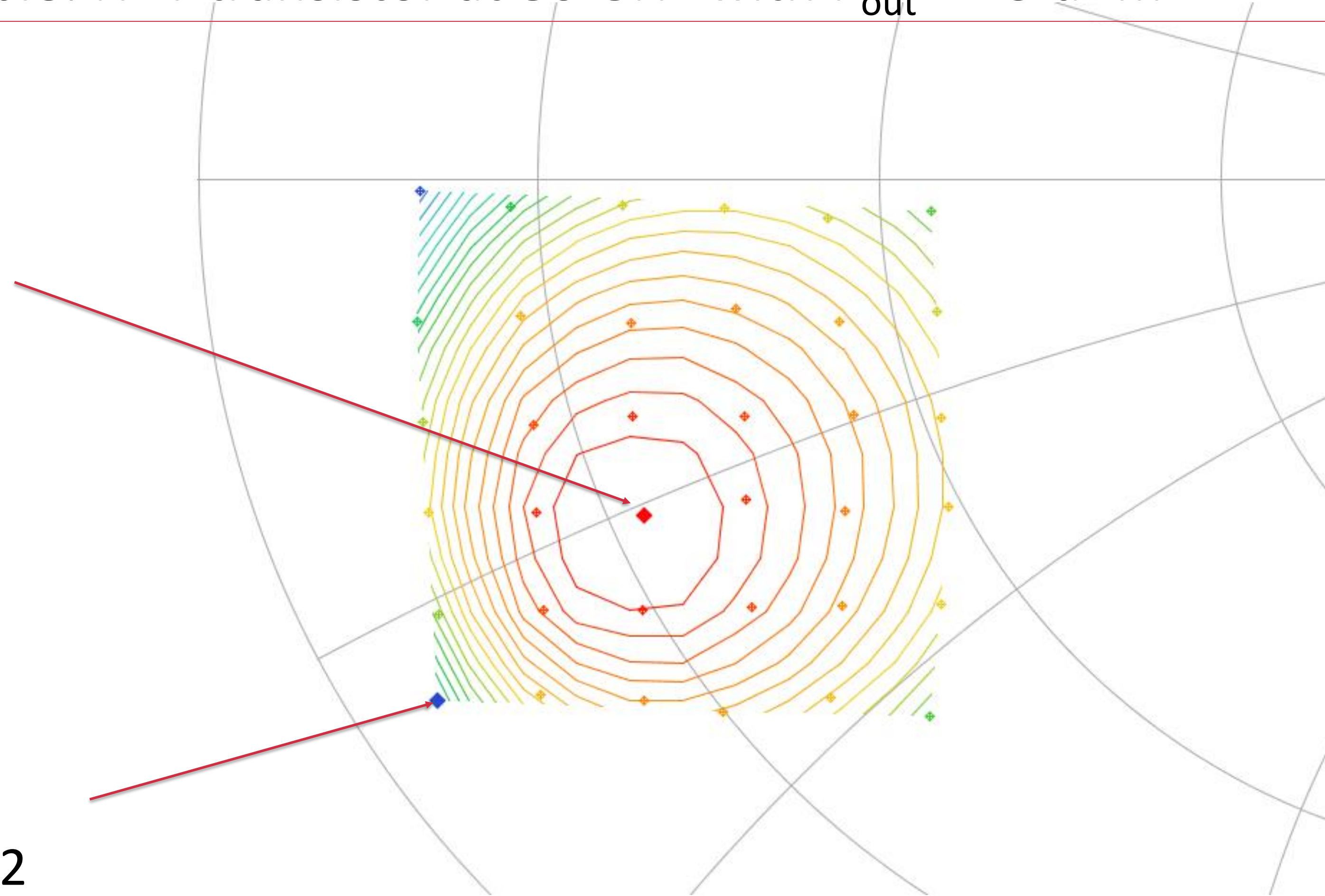
# Waveguide passive and hybrid-active LP measurements

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Example: HBT transistor at 80 GHz with  $P_{out} = 15$  dBm

Optimum Eff  
 $|\Gamma| \rightarrow 0.68$

Closed contours  
 $|\Gamma| \rightarrow 0.92$





- ## How:

- ## Why:

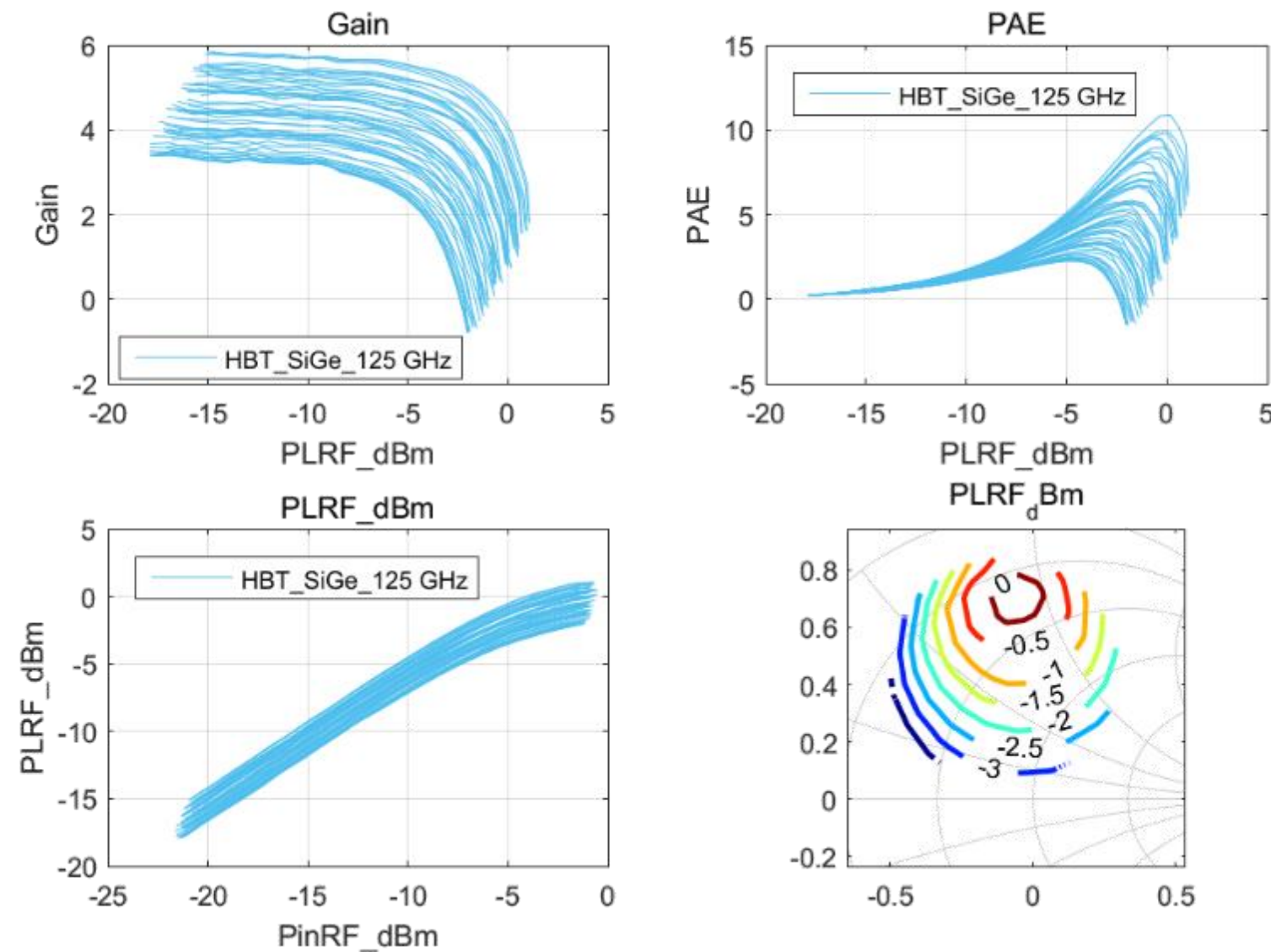
- Power controlled S-parameters
- Fundamental active load-pull



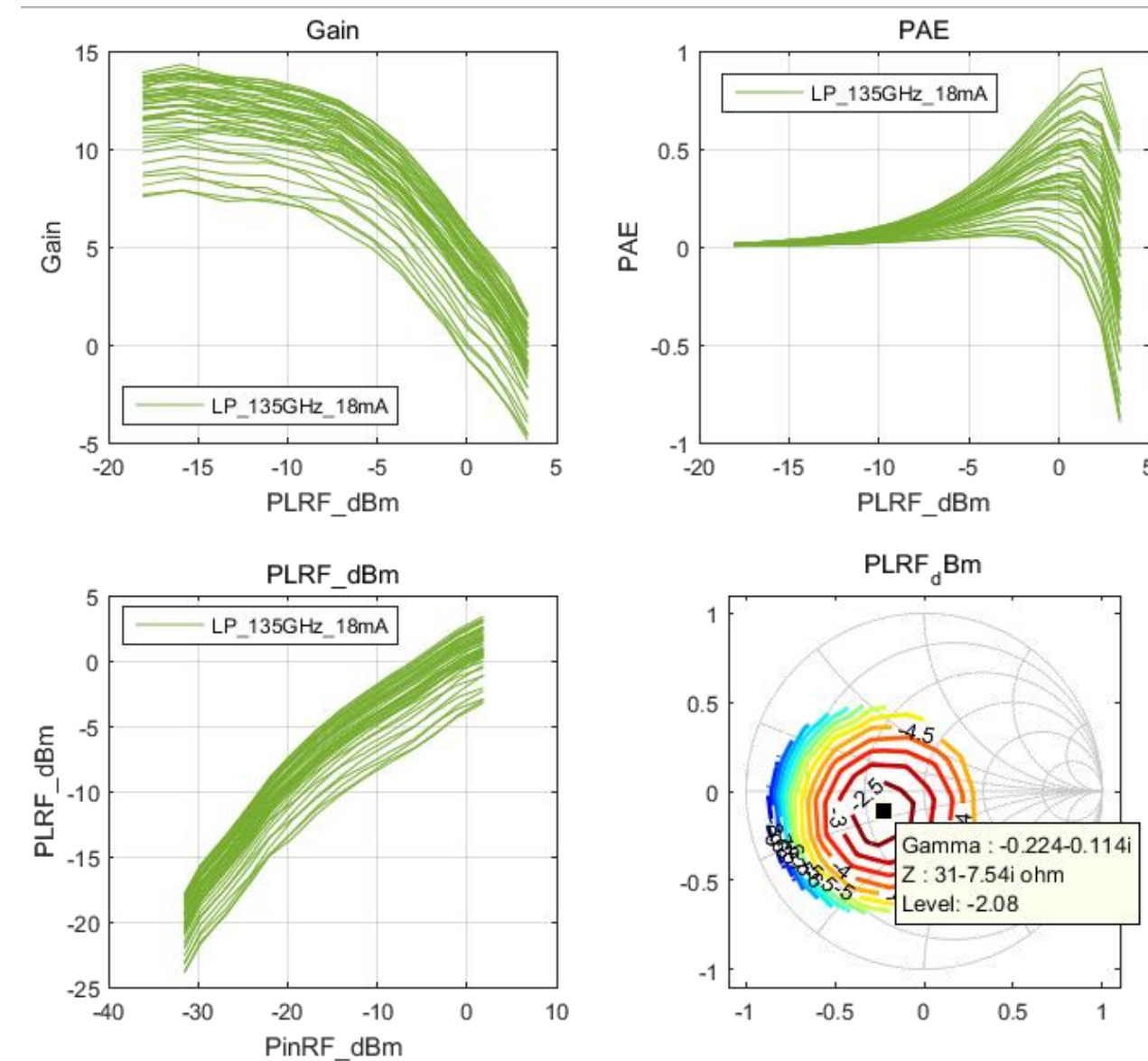




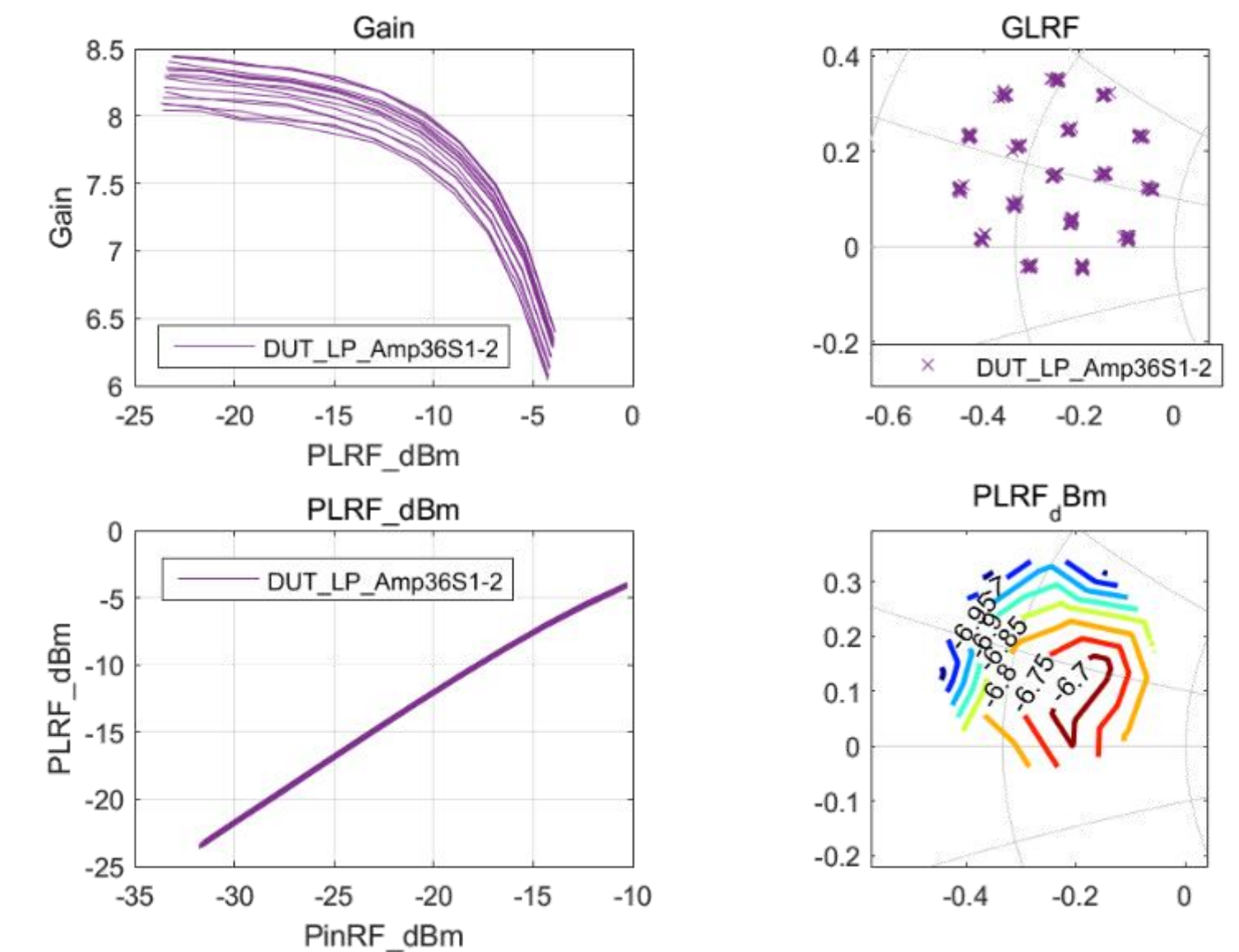
Characterization of **small-cells**: SiGe 130 nm double finger HBT at 125 GHz



Characterization of on-wafer **multi-stage** PA: SiGe BiCMOS at 135 GHz



Characterization of on-wafer **multi-stage** PA at 250 GHz



# Thank You!

